

**Theoretical design of high-performance
thermoelectric materials and unconventional
superconductors using first-principles calculations**

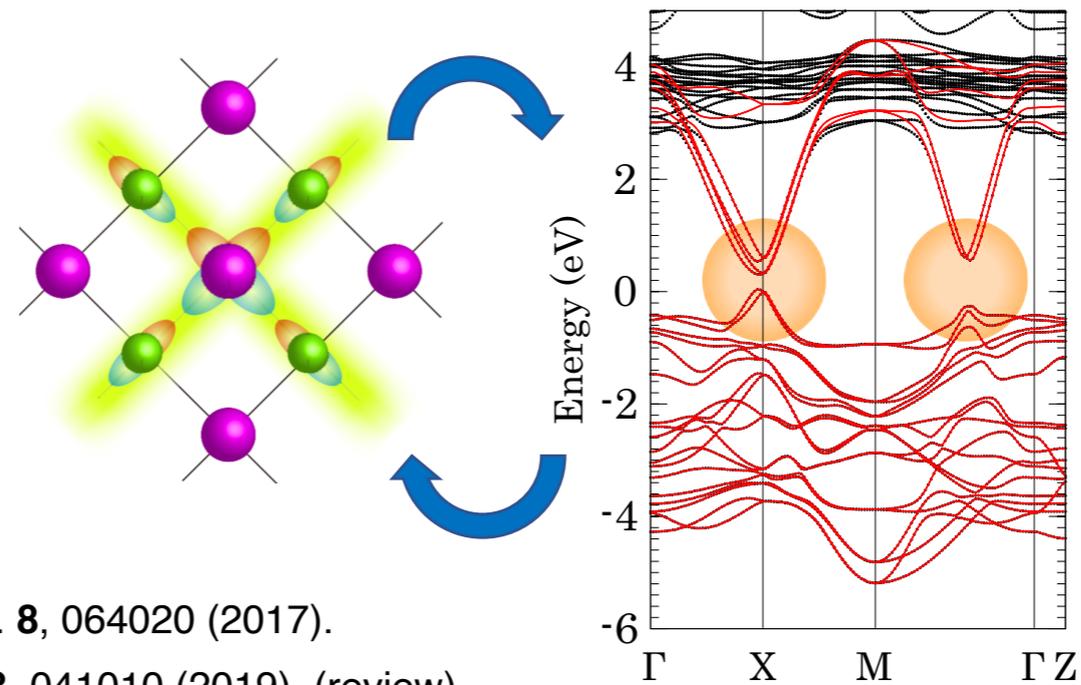
Masayuki Ochi

Department of Physics, Osaka University

Self-introduction

Name	Masayuki Ochi
Biography	2009–2014 Dept. Phys, The Univ. of Tokyo 2014–2015 PD researcher in RIKEN CEMS 2015–present Research Associate in Dept. Phys, Osaka Univ.
Research Interest	Thermoelectrics Strongly correlated materials Topological phases Wave function theory

Part 1 : High thermoelectric performance by quasi-1dim gapped Dirac cone



MO, H. Usui, and K. Kuroki, PRApl. **8**, 064020 (2017).

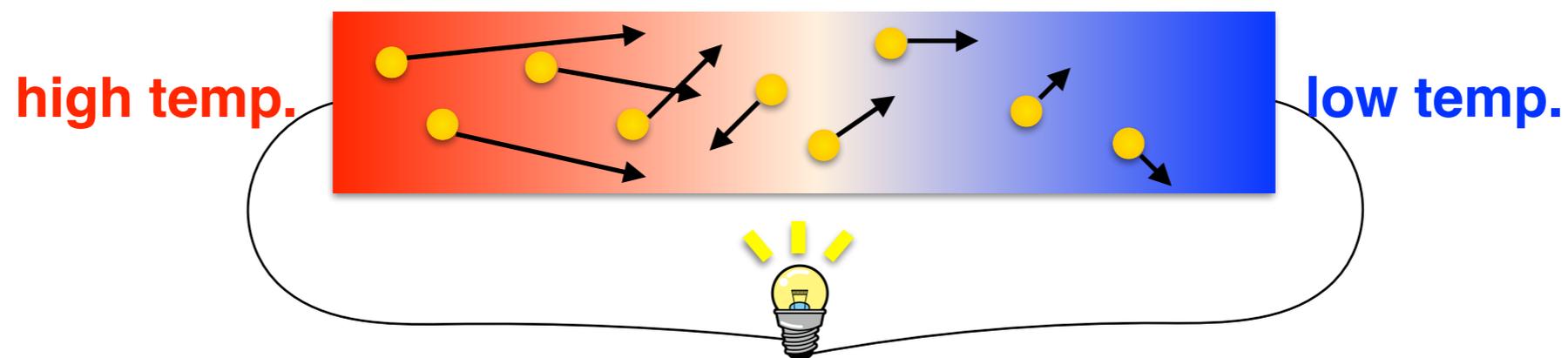
MO, H. Usui, and K. Kuroki, JPSJ **88**, 041010 (2019). (review)

[Collaborators] Hidetomo Usui (Shimane Univ.), Kazuhiko Kuroki (Osaka Univ.)

Thermoelectric conversion (Thermoelectric effect)

= direct conversion of temperature difference to electric voltage and vice versa

(e.g.) Seebeck effect

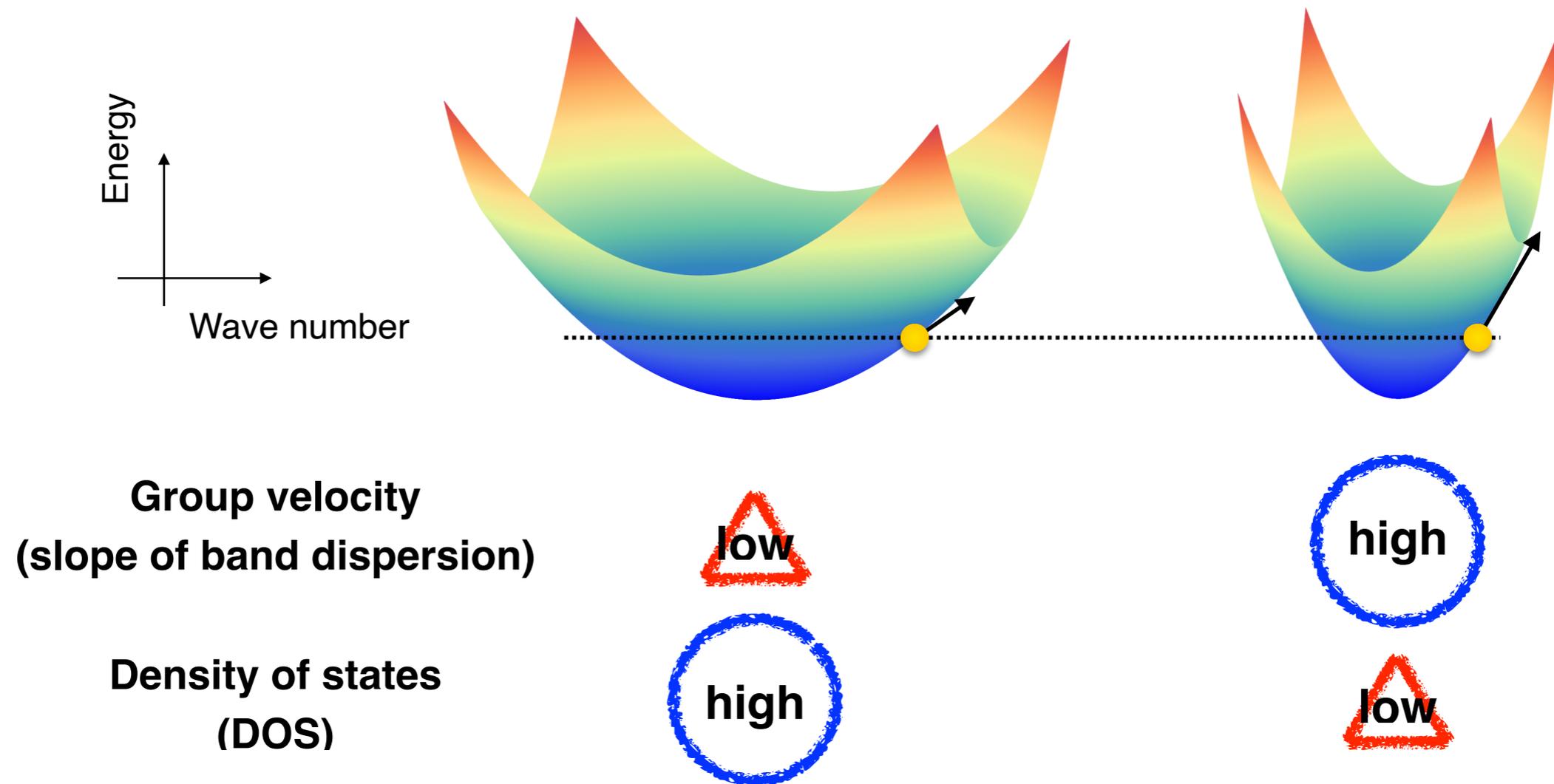


$$V = -S\Delta T \text{ (V:voltage, S: Seebeck coeff., } \Delta T: \text{ temperature diff.)}$$

enables a use of waste heat as energy resource = **clean energy**

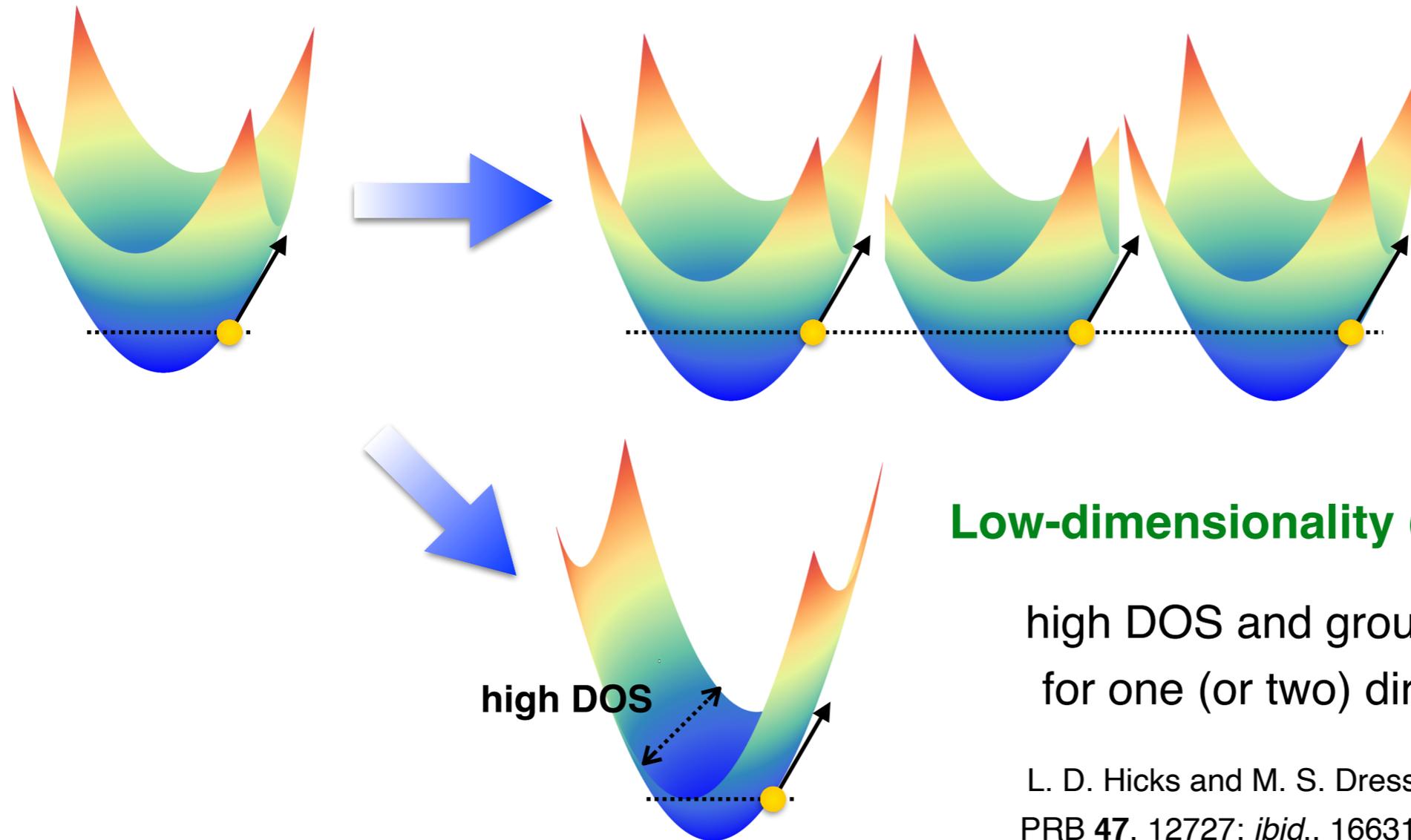
Efficient conversion is a key for application

Electronic band structure for thermoelectric effects



Trade-off relation for a simple band dispersion

Characteristic band shapes in good thermoelectric materials



Multi valley

large DOS by
valley degeneracy

Y. Pei *et al.*,
Nature **473**, 66 (2011).

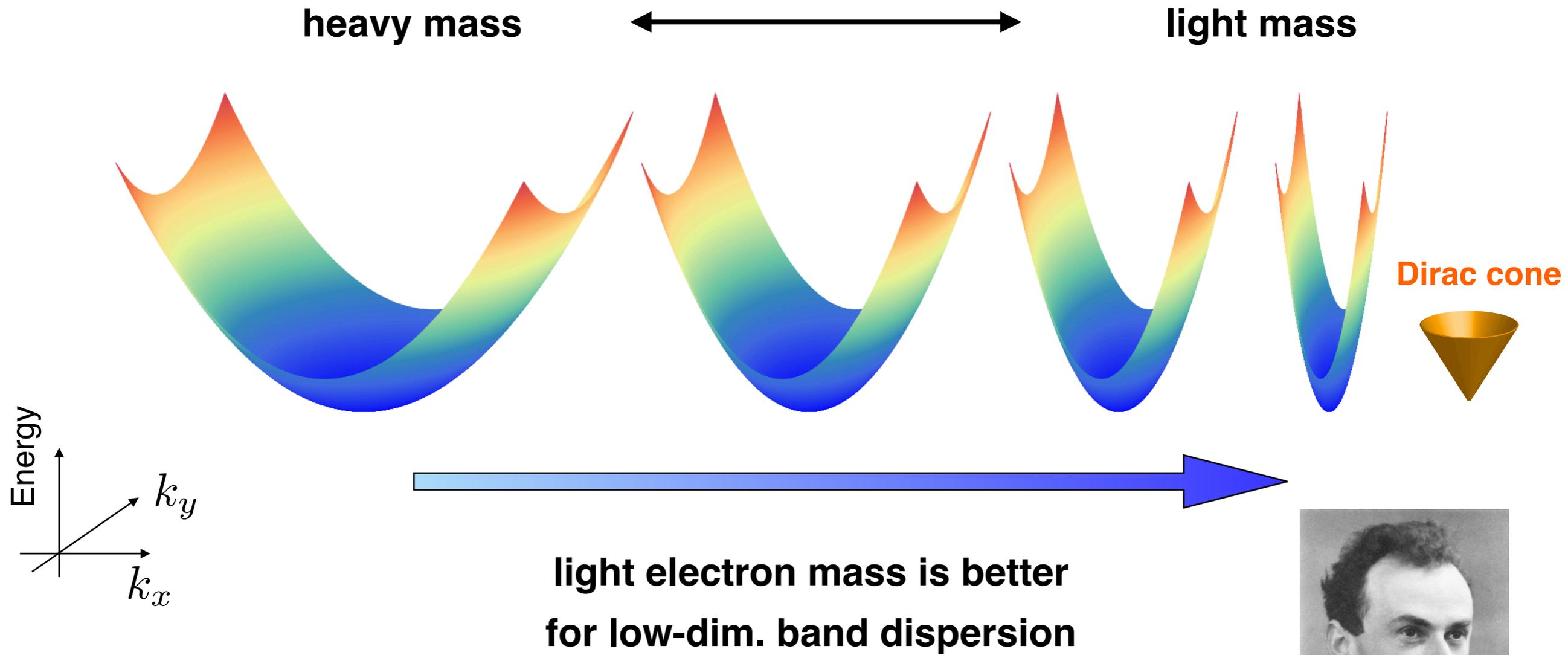
Low-dimensionality (anisotropy)

high DOS and group velocity
for one (or two) direction(s)

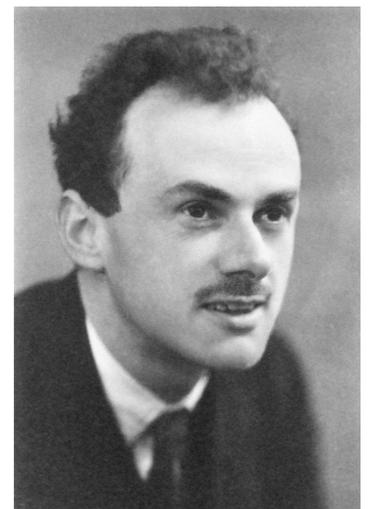
L. D. Hicks and M. S. Dresselhaus,
PRB **47**, 12727; *ibid.*, 16631 (1993).

**Characteristic band dispersion can enhance
thermoelectric conversion efficiency**

Further optimization of low-dim. band

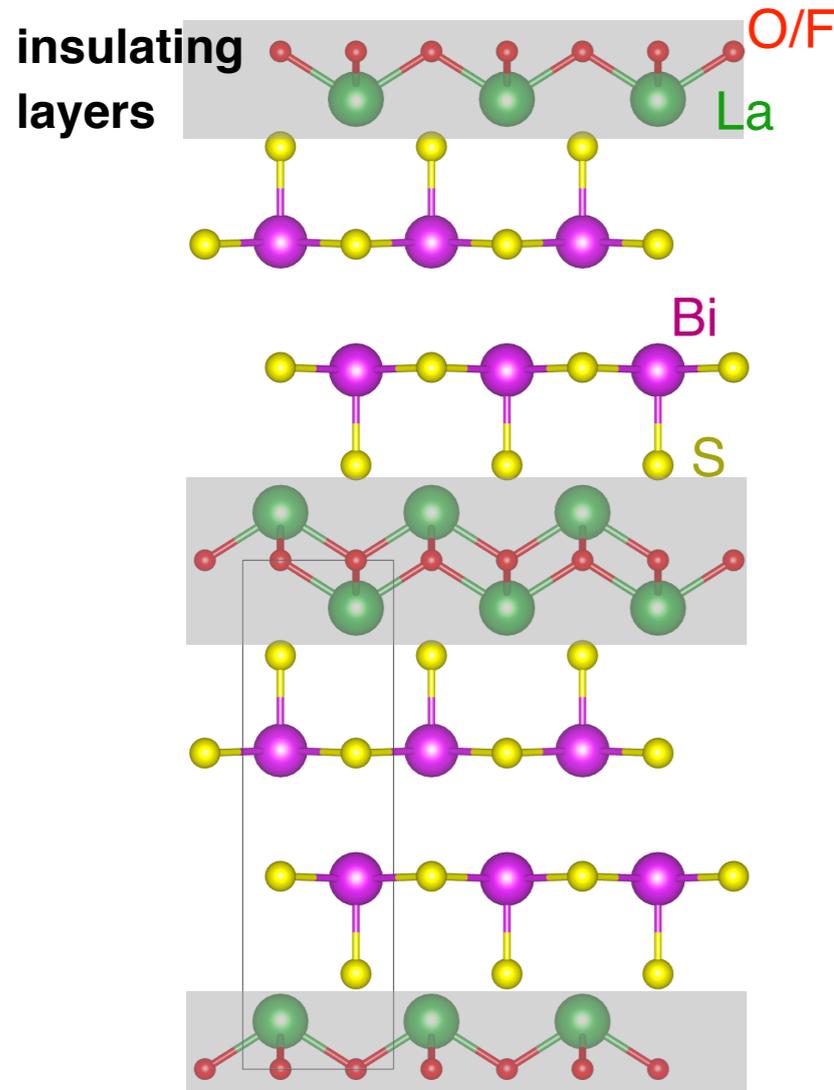


Can we find such a band dispersion in real materials?



Paul Dirac
© Wikipedia

BiS₂ layered materials



known as superconductors

Y. Mizuguchi *et al.*, PRB **86**, 220510 (2012).

Y. Mizuguchi *et al.*, JPSJ **81**, 114725 (2012).



High controllability (chemical pressure, carrier doping, etc)

recently paid attention as thermoelectric materials

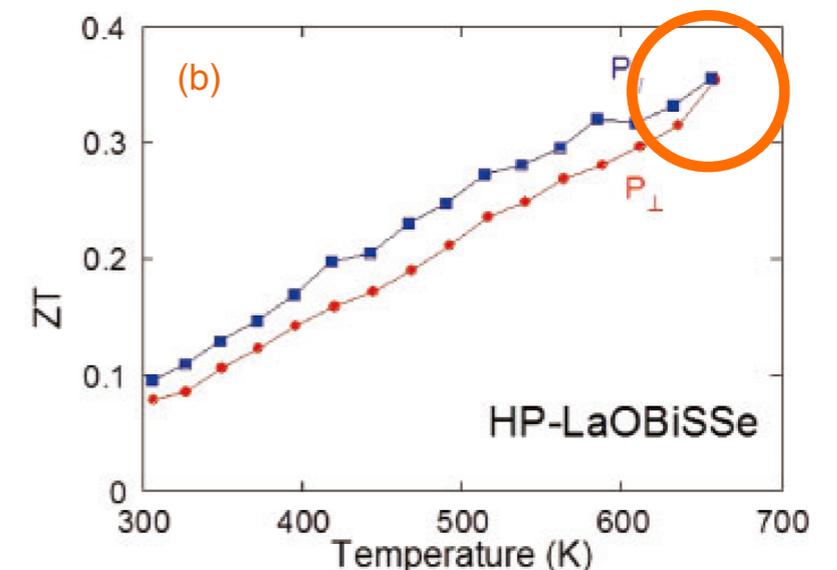
Low thermal conductivity

$$\kappa_{\text{lattice}} \sim 1 \text{ W/m/K} @ T = 300 \text{ K}$$

Relatively high ZT

* ZT = a measure of conversion efficiency

A. Nishida *et al.*, Appl. Phys. Express **8**, 111801 (2015).



We find that BiS₂ layered materials can be a platform of **ideal electronic structure** for thermoelectric effects: **low-dim. + gapped Dirac cone + multi-valley**, by appropriate atomic substitution

Calculation details

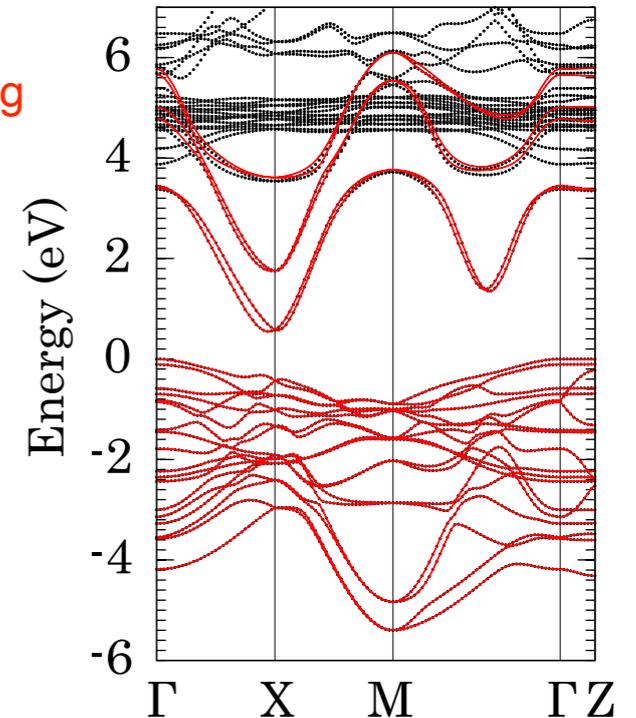
DFT band calc. and Wannierization (Bi,O,S-p orbitals)

- WIEN2k for band calc.
- modified Becke-Johnson potential (known to give a relatively accurate band gap)
- wien2wannier and Wannier90 for Wannierization

$$\mathcal{H} = \sum_{ij} t_{ij} c_i^\dagger c_j$$

Tight-binding model: electron transfer between Wannier functions (spatially localized orbitals)
= transfer integrals are determined so as to reproduce first-principles band dispersion

Black lines: First-principles
Red lines: Wannier tight-binding



Wannier is used for getting physical insight, taking a (very) fine k-mesh, etc.

$\epsilon_{n,\mathbf{k}}$



Boltzmann transport theory

- constant relaxation time (τ) approximation
- rigid band approximation for carrier doping

$$\sigma = e^2 \mathbf{K}_0, \quad \mathbf{S} = -\frac{1}{eT} \mathbf{K}_0^{-1} \mathbf{K}_1, \quad \kappa_{\text{el}} = \frac{1}{T} (\mathbf{K}_2 - \mathbf{K}_1 \mathbf{K}_0^{-1} \mathbf{K}_1),$$

$$\mathbf{K}_\nu = \tau \sum_{\mathbf{k},n} \mathbf{v}_{\mathbf{k},n} \otimes \mathbf{v}_{\mathbf{k},n} \left[-\frac{\partial f_0(\epsilon_{\mathbf{k},n}, T)}{\partial \epsilon} \right] (\epsilon_{\mathbf{k},n} - \mu(T))^\nu$$

σ : electrical conductivity

\mathbf{S} : Seebeck coefficient

κ_{el} : electrical thermal conductivity

A bit more about Boltzmann transport theory

For example, electrical conductivity along the x direction is given as follows:

$$\sigma_{xx} \propto \tau \sum_{\mathbf{k}, \mathbf{n}} v_{x;(\mathbf{k}, \mathbf{n})}^2 \left[-\frac{\partial f_0(\epsilon_{\mathbf{k}, \mathbf{n}}, T)}{\partial \epsilon} \right]$$

see how σ depends on several quantities...

\mathcal{T} relaxation time (time length between electron scatterings)

: long relaxation time yields high electrical conductivity

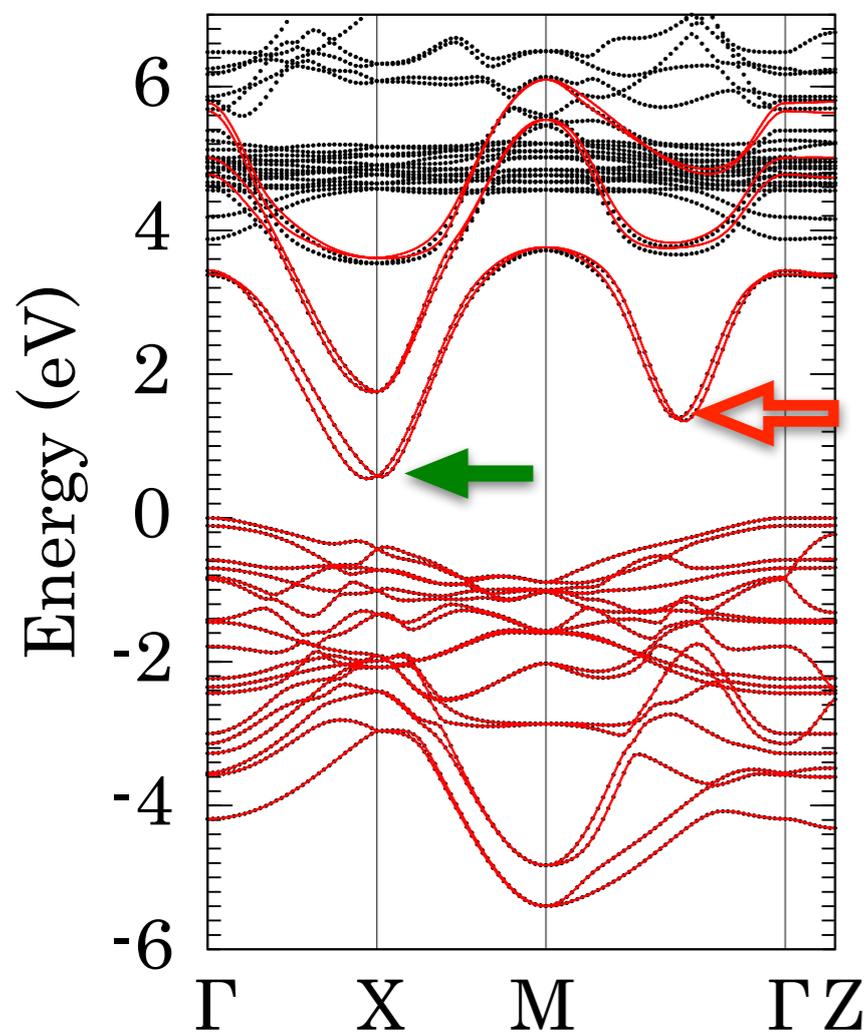
$v_{x;(\mathbf{k}, \mathbf{n})}^2$ square of group velocity of the n -th band at a certain \mathbf{k} point

: high group velocity yields high electrical conductivity

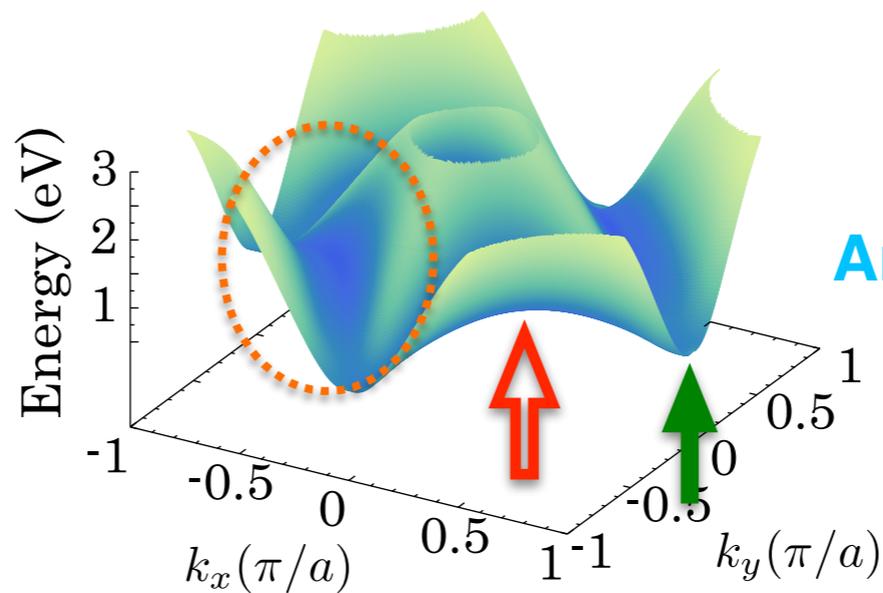
$-\frac{\partial f_0(\epsilon_{\mathbf{k}, \mathbf{n}}, T)}{\partial \epsilon}$ derivative of the Fermi-Dirac distribution (having a sizable value only near $\mu = \epsilon$)

: only Kohn-Sham states near the Fermi level can contribute to the electrical conductivity

LaOBiS₂: electronic structure



* consider a small amount of electron carrier, i.e., near the bottom of the conduction band (shown by arrows)

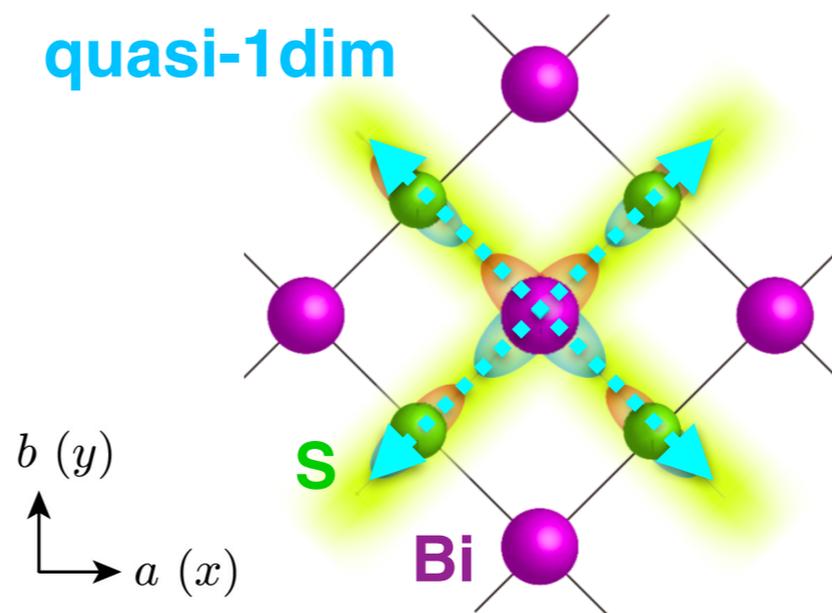


k_x - k_y plot for the lowest conduction band

Anisotropy of the slope



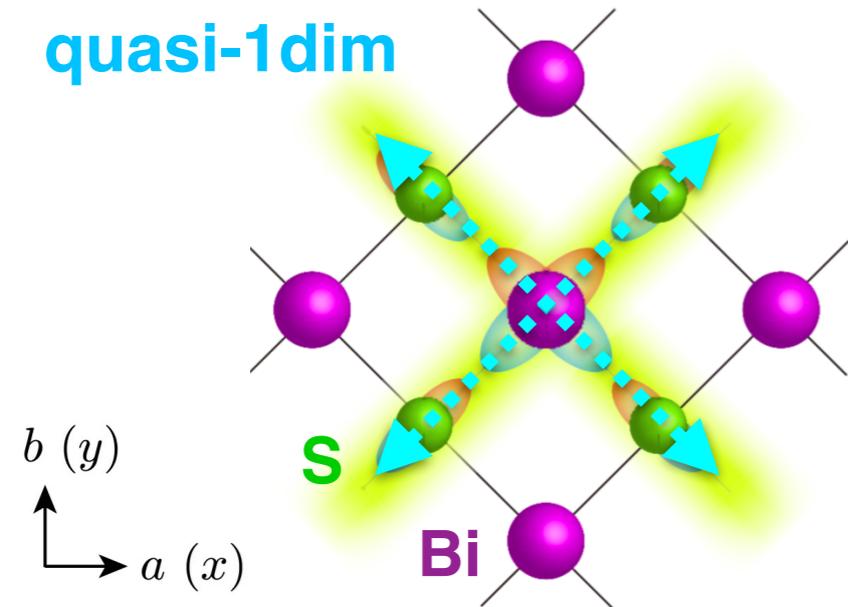
quasi-1dim



Low-dimensionality
by orbital anisotropy

cf. H. Usui *et al.*, PRB **86**, 220501(R) (2012).

What weakens anisotropy



Several factors **weaken quasi-one dimensionality**

1. Spin-orbit coupling (relativistic effect)

→ hybridization between p_x and p_y

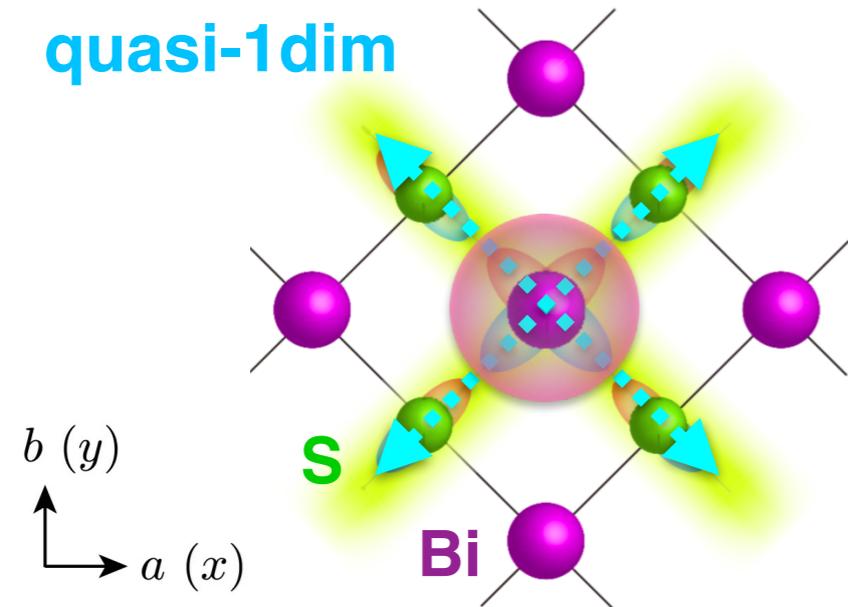
2. Electron transfer among Bi orbitals

* conduction bands mainly consist of Bi orbitals

3. Energy difference between Bi and S orbitals

→ large energy difference prevents electron transfer

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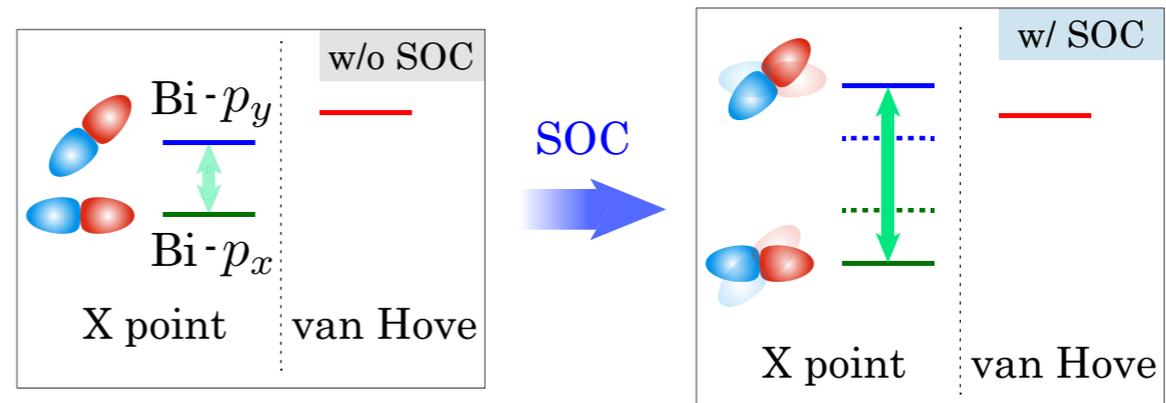
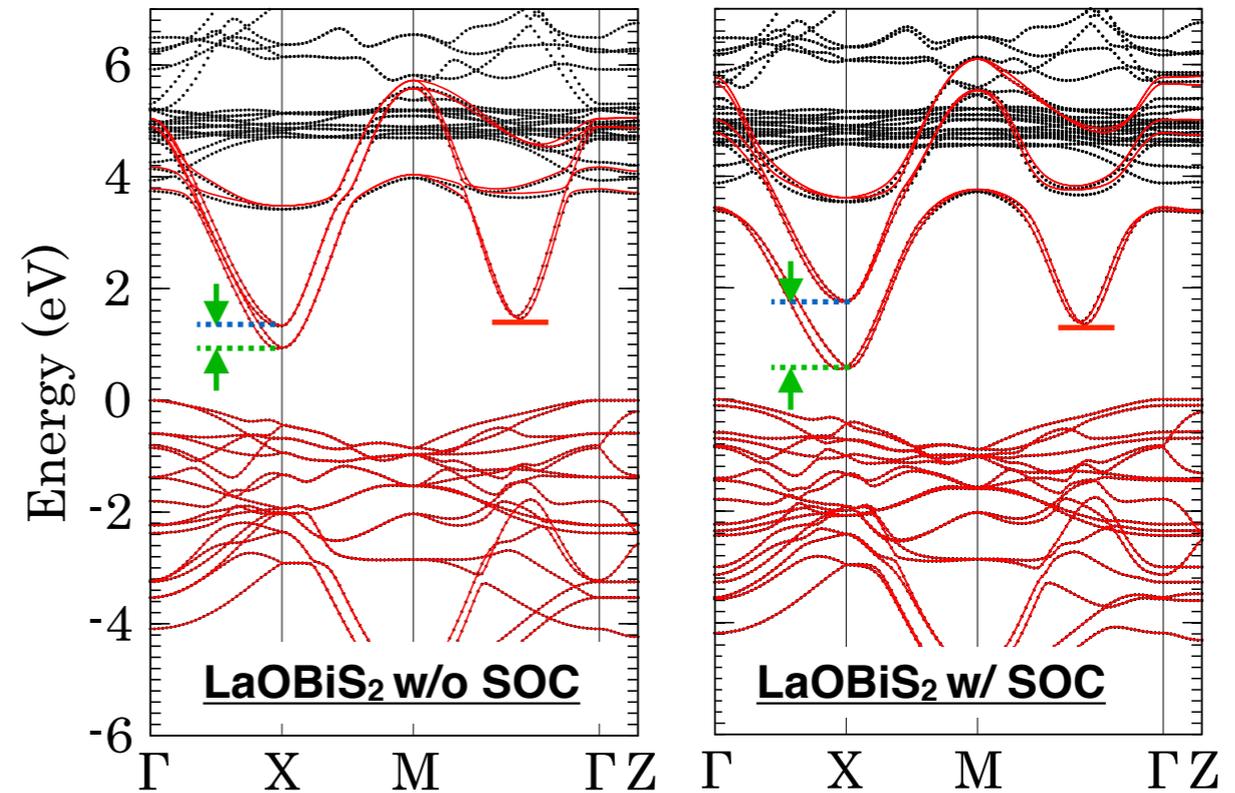
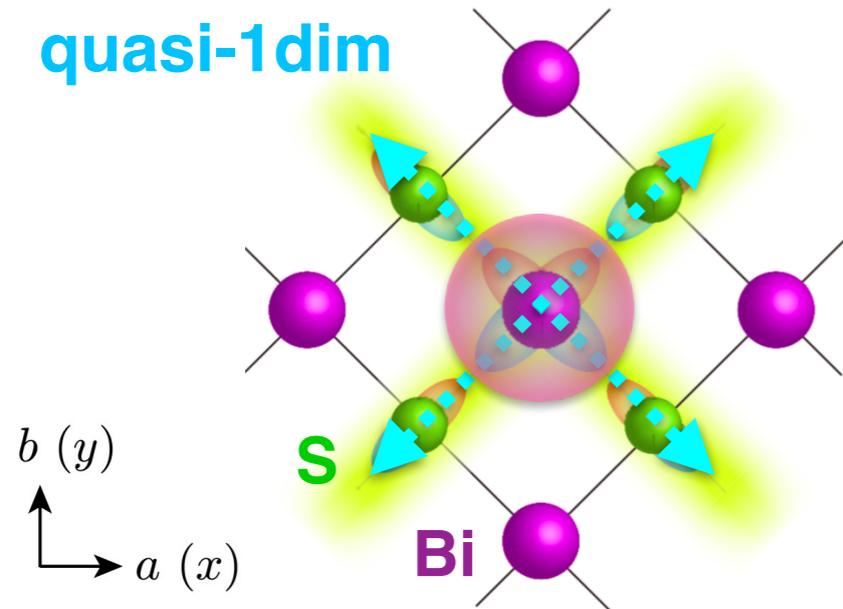
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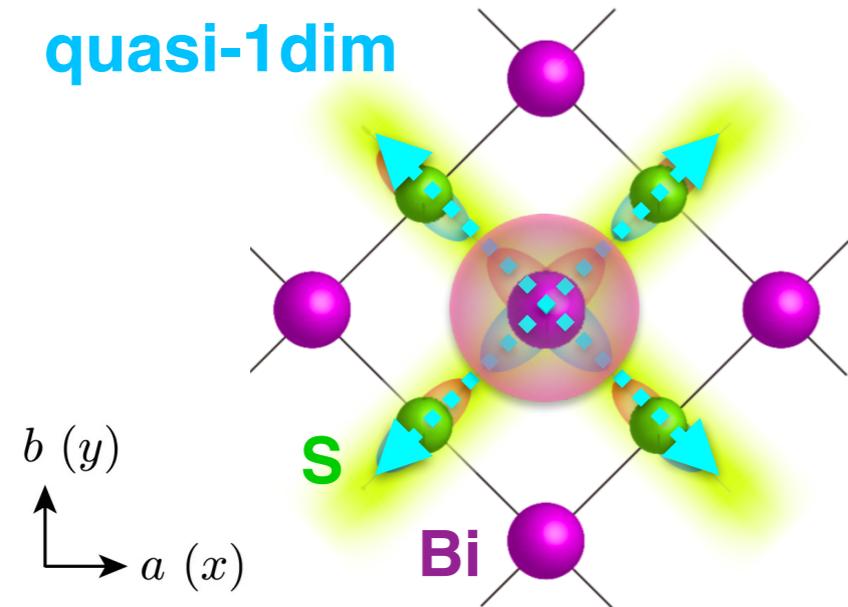
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Spin-orbit coupling (SOC)



van Hove singularity gets farther from the band edge
(i.e. low-dim is weakened) by SOC band splitting

What weakens anisotropy



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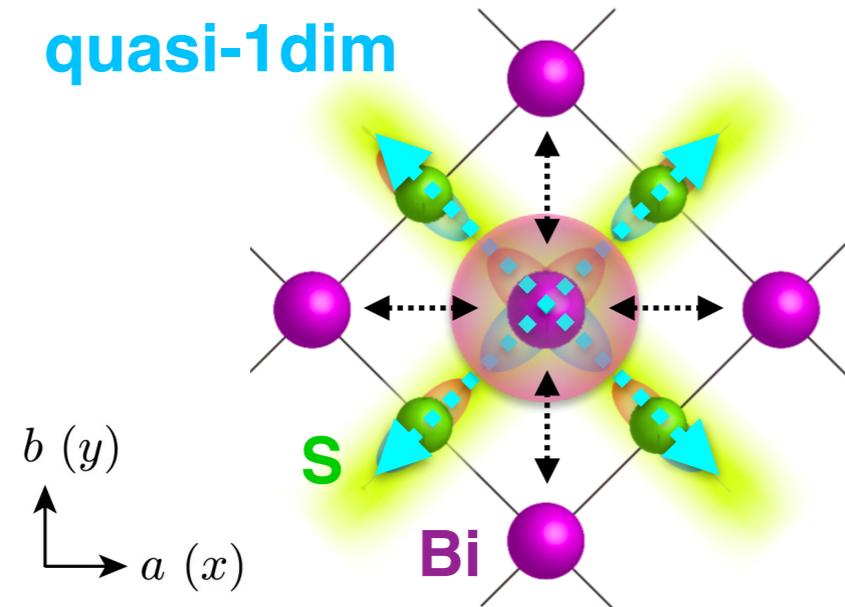
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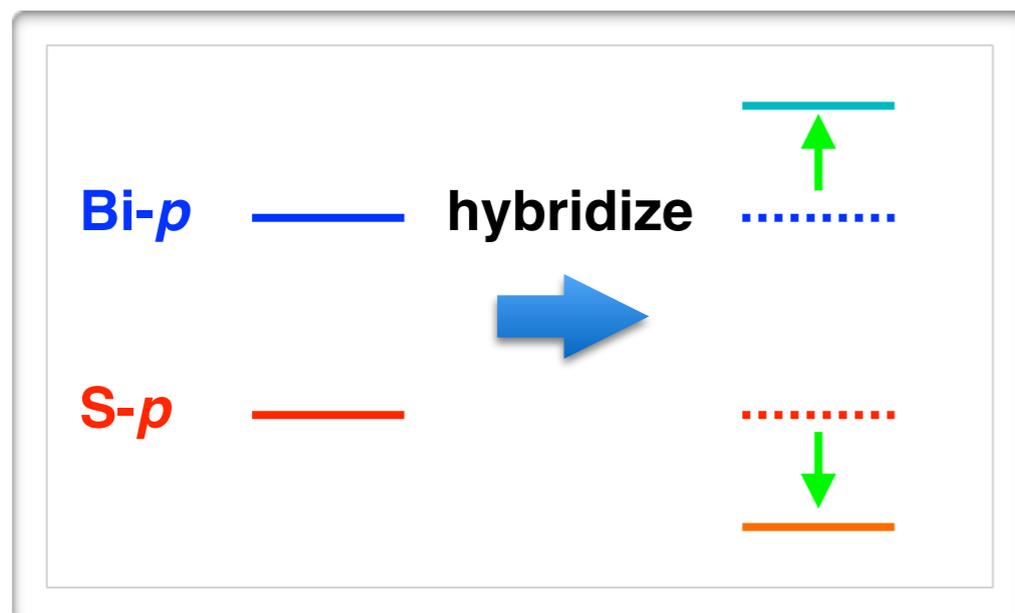
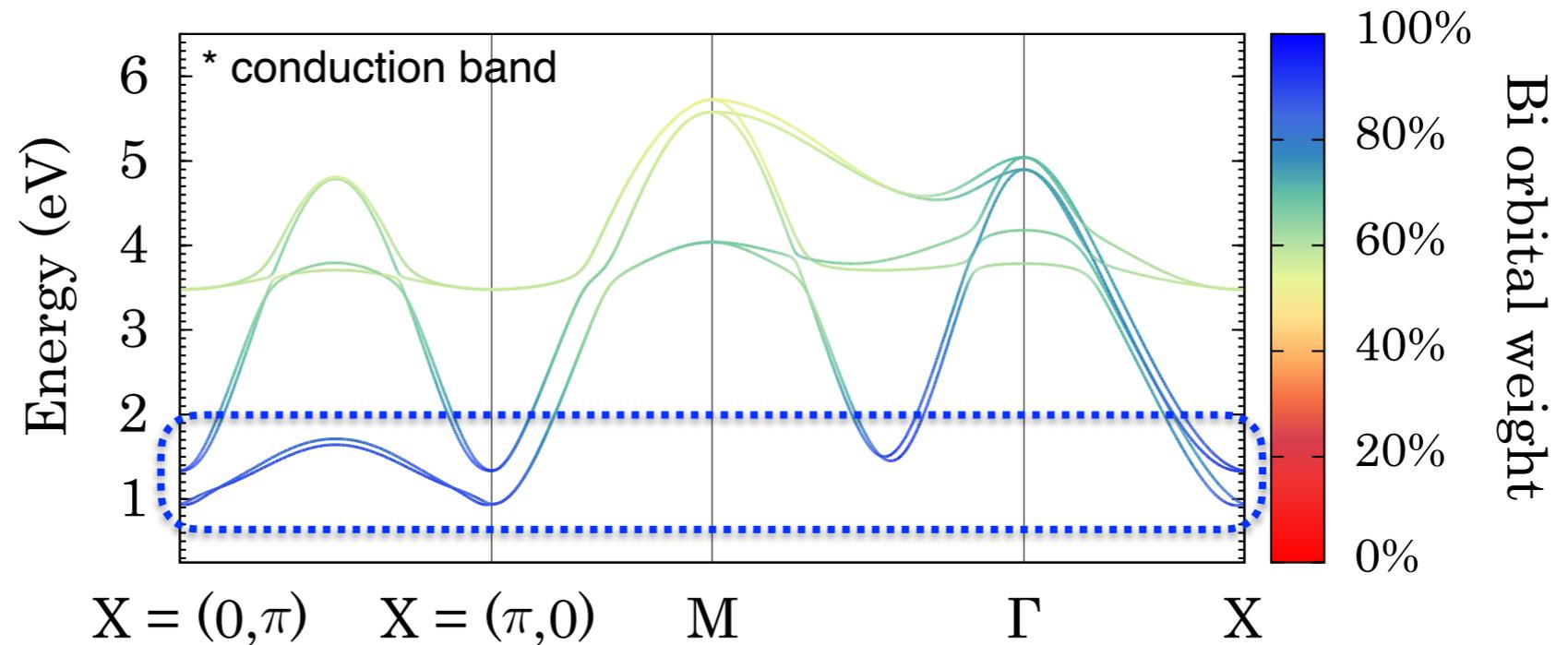
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Bi orbital weight

LaOBiS₂ / no SOC

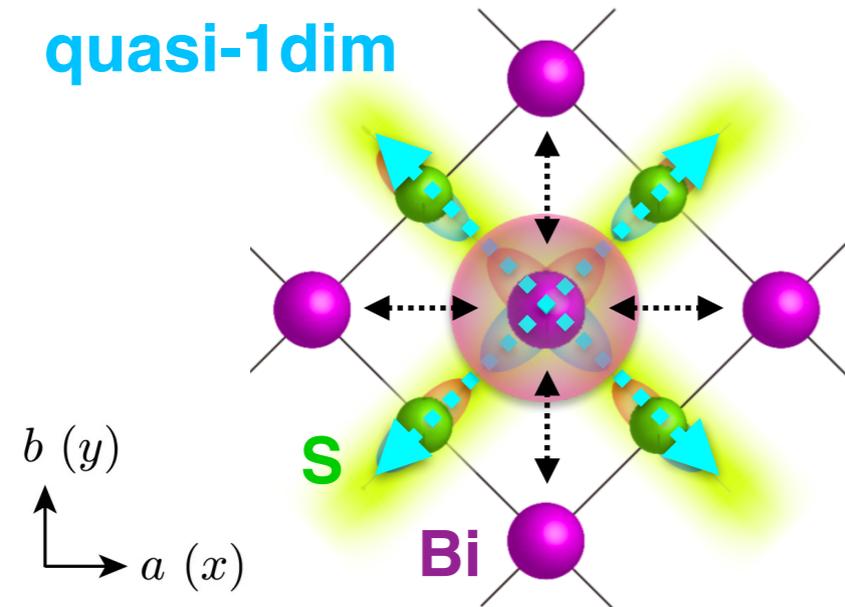
mainly Bi orbitals



If hybridization is strong at a certain k-point, the anti-bonding Bi bands should have a high energy (and a sizable S orbital weight)

On the other hand, the anti-bonding Bi bands **near** the band edge should have little S weight

What weakens anisotropy



Several factors **weaken quasi-one dimensionality**

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→ hybridization between p_x and p_y

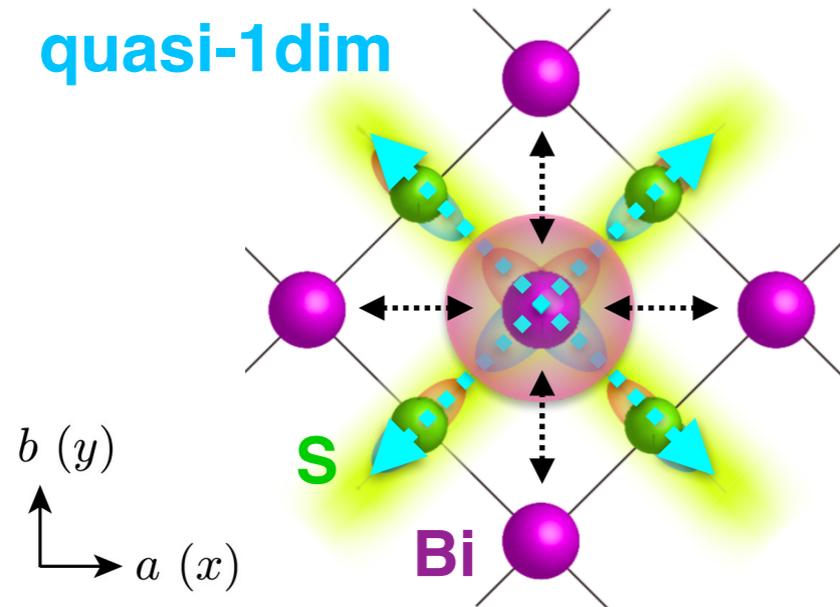
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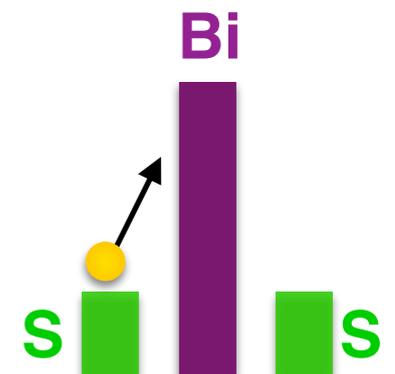
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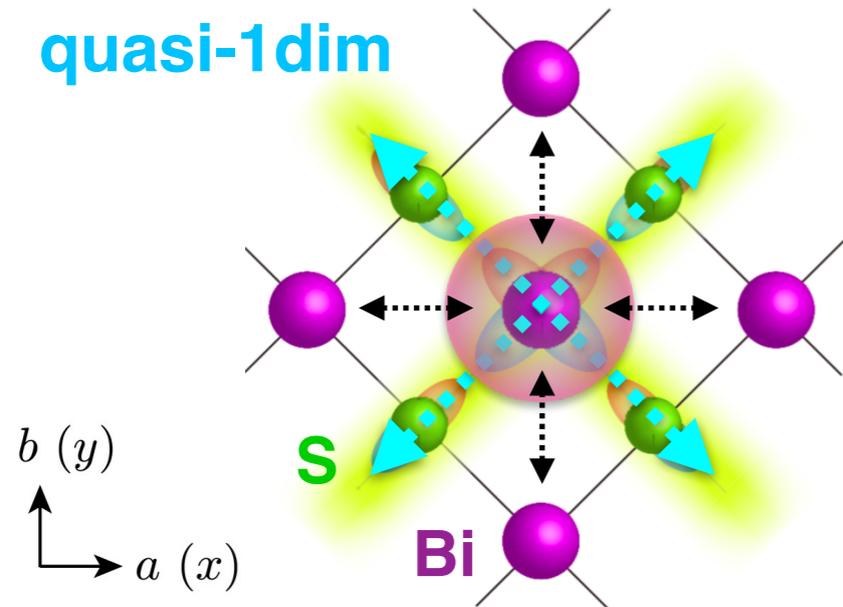
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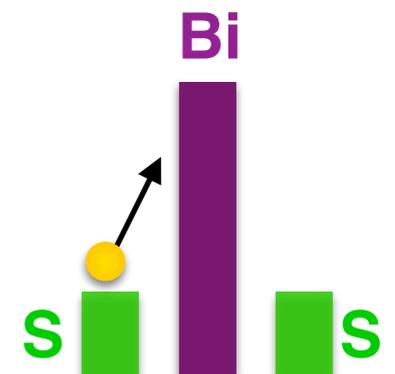
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Quasi-one dim. can be enhanced by atomic substitution

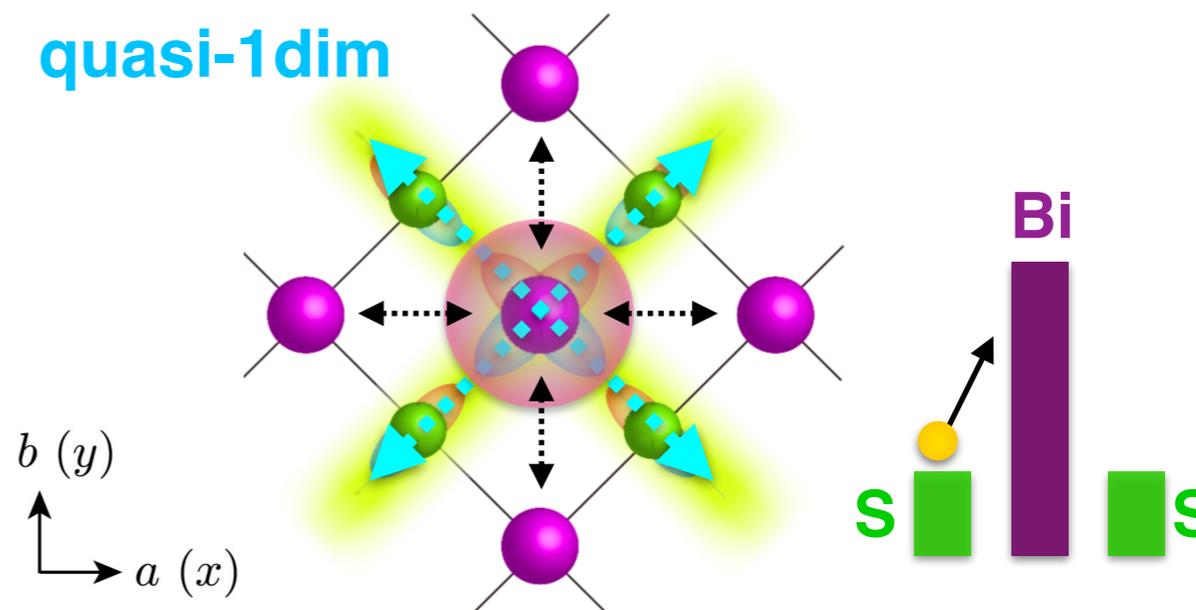
MO *et al.*, PRAppl. **8**, 064020 (2017).



Band engineering

14		15	16	17	18
		Pnictogens	Chalcogens	ハロゲン	
		273			2 He ヘリウム 4.0026
6 C 炭素 12.011	7 N 窒素 14.007	8 O 酸素 15.999	9 F フッ素 18.998	10 Ne ネオン 20.180	
14 Si ケイ素 28.085	15 P リン 30.974	16 S 硫黄 32.06	17 Cl 塩素 35.45	18 Ar アルゴン 39.948	
32 Ge ゲルマニウム 72.630	33 As ヒ素 74.922	34 Se セレン 78.971	35 Br 臭素 79.904	36 Kr クリプトン 83.798	
50 Sn スズ 118.71	51 Sb アンチモン 121.76	52 Te テルル 127.60	53 I ヨウ素 126.90	54 Xe キセノン 131.29	
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114	115	116	117	118	

quasi-1dim



1. Spin-orbit coupling (Relativistic effect)

→ use a light Pnictogen (than Bi)

2. Electron transfer among Bi orbitals

→ use a light Pnictogen and heavy chalcogen

3. Energy difference between Bi and S orbitals

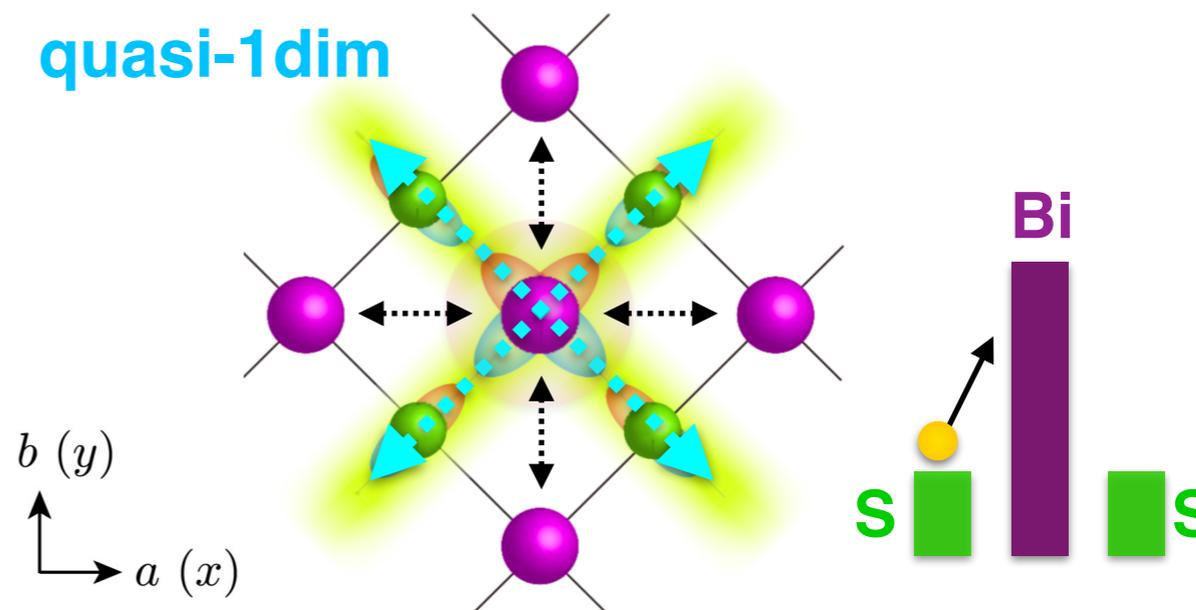
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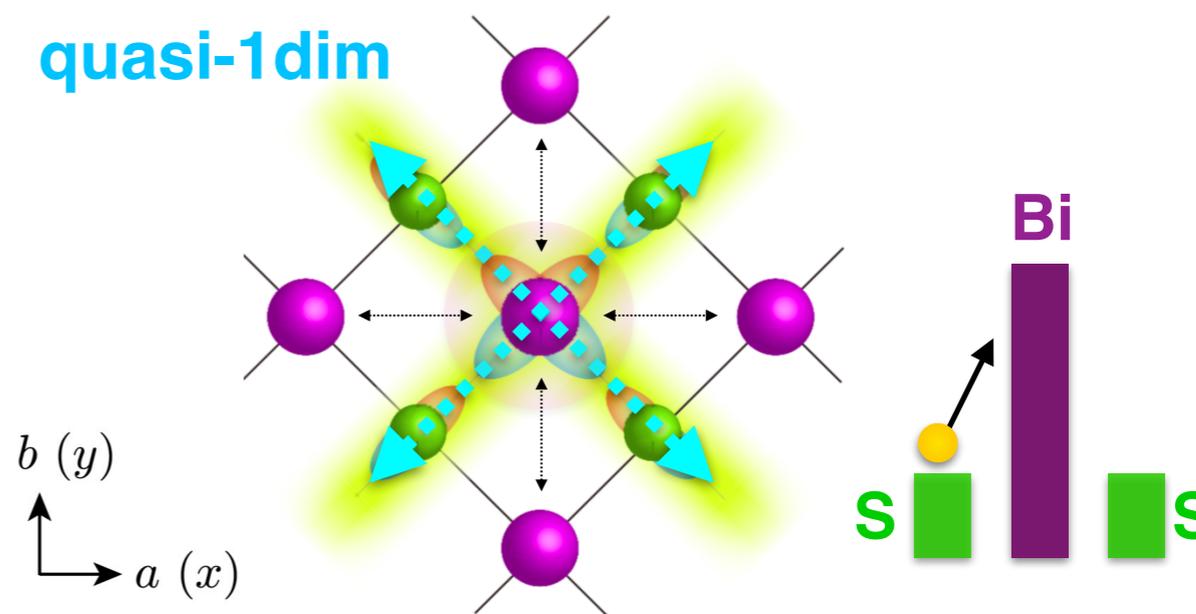
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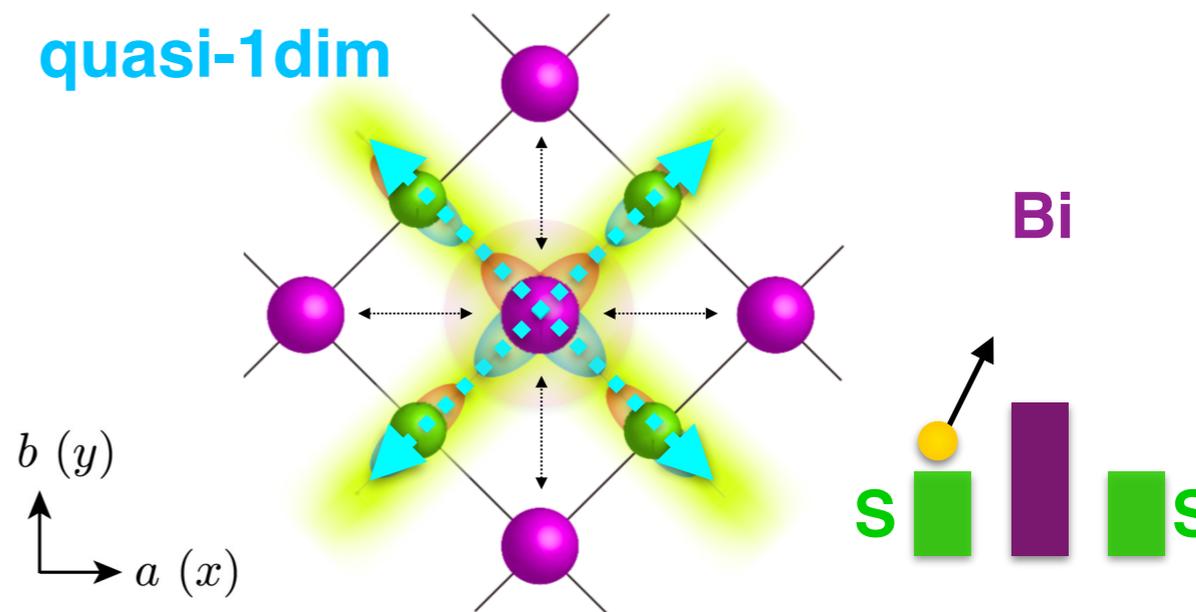
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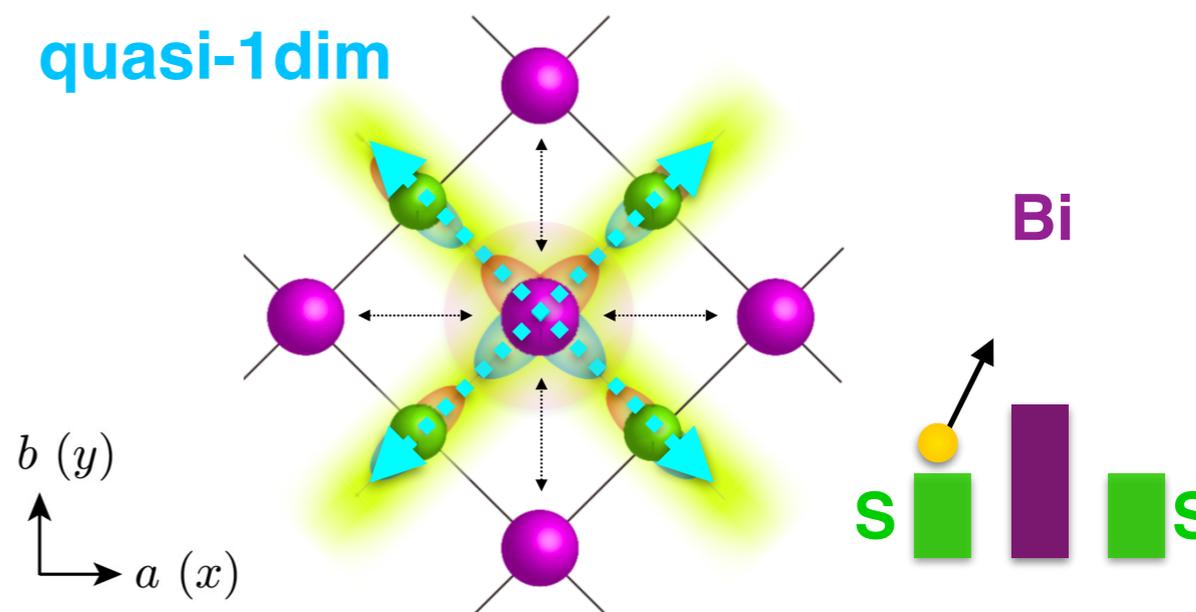
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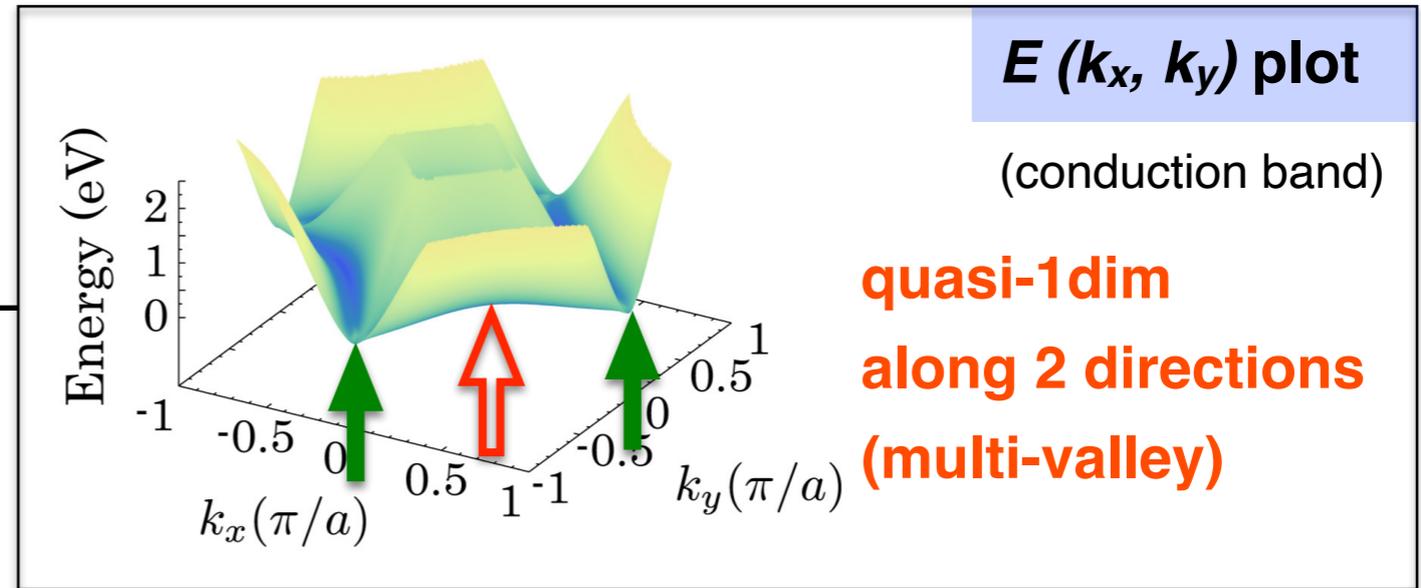
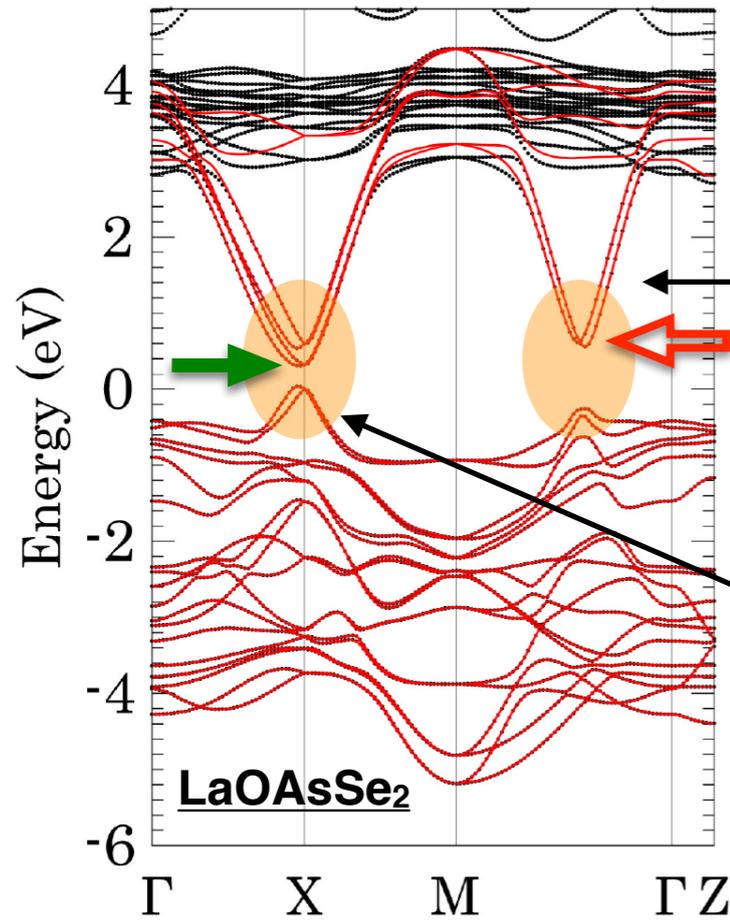
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MO *et al.*, PRAppl. 8, 064020 (2017).

Ideal electronic structure: quasi-1dim gapped Dirac cone

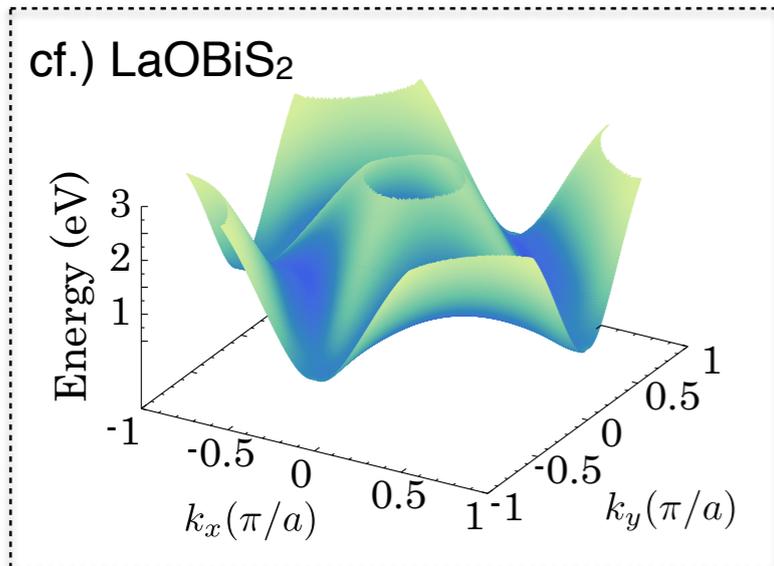


gapped Dirac cone

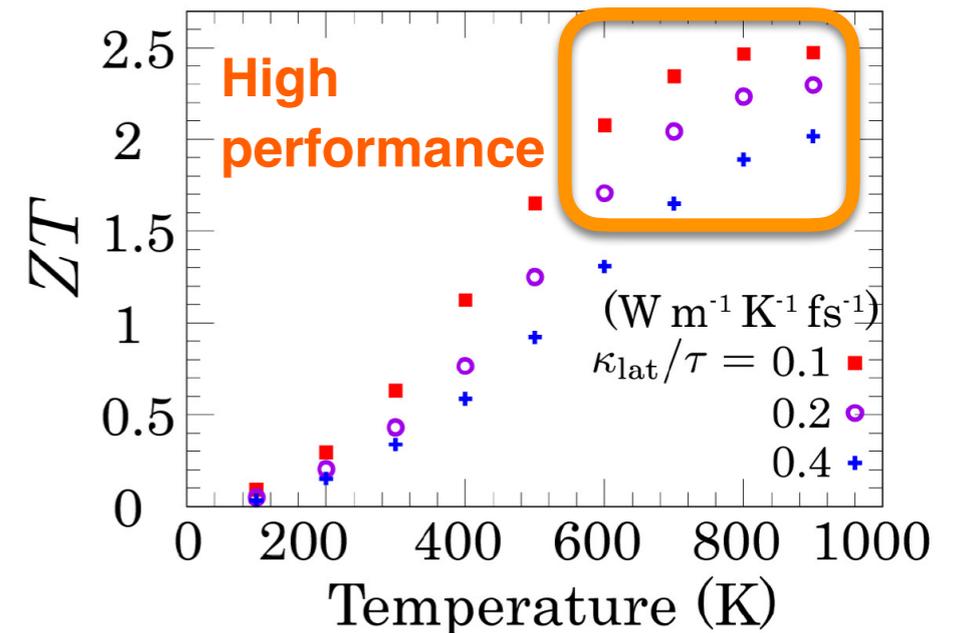
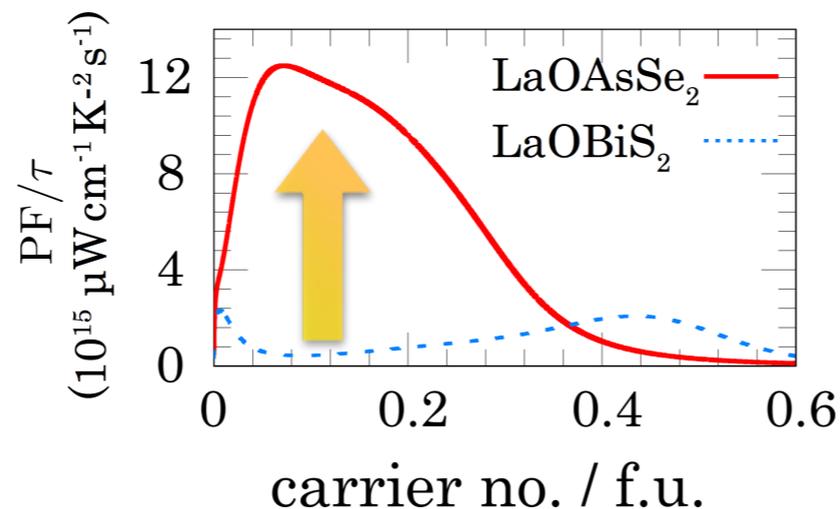
One of the ideal band dispersion

* gap = prevents electron & hole cancelation

$$ZT = \sigma S^2 T / \kappa$$

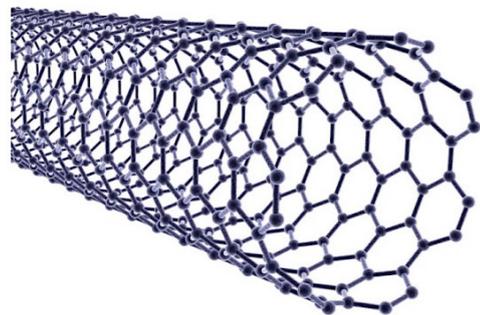


$$PF = \sigma S^2$$



Relation to other thermoelectric materials

Carbon nanotube



1dim (gapped) Dirac cone

high mobility but high thermal conductivity

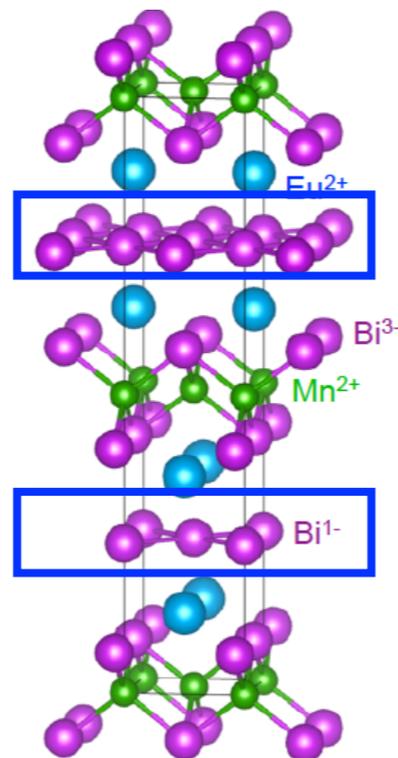
R. S. Prasher *et al.*, PRL **102**, 105901 (2009). Y. Nakai *et al.*, Appl. Phys. Express **7**, 025103 (2014). T. Yamamoto and H. Fukuyama, JPSJ **87**, 024707 (2018); *ibid.* 114710 (2018).

AMnBi₂ (A = Ca, Sr, Eu)

also have a $p_{x,y}$ network on the Bi square lattice

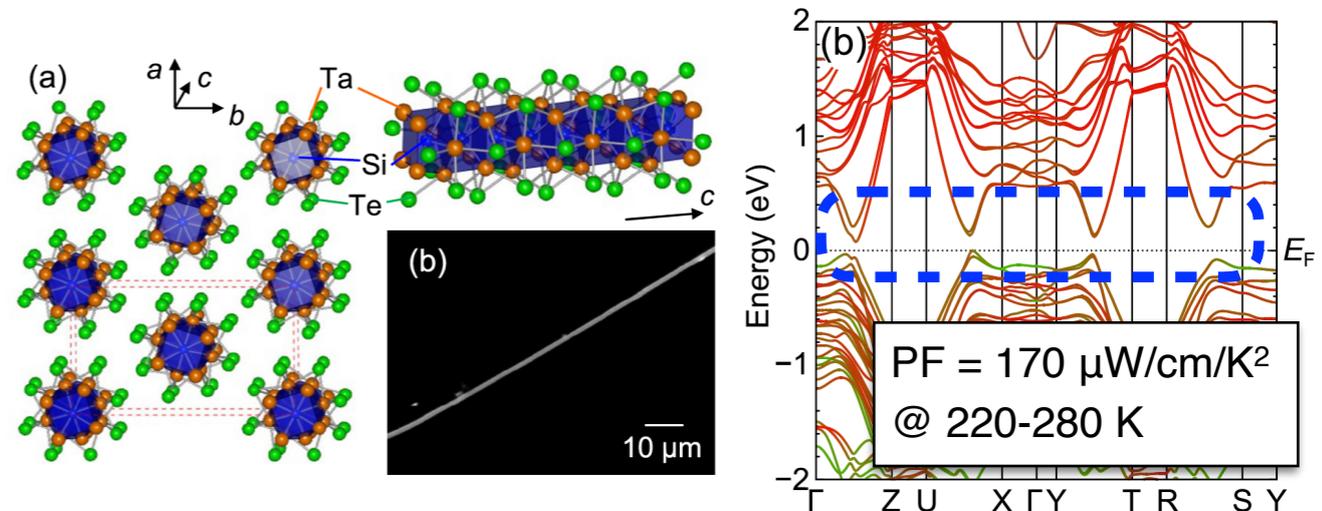
→ quasi-1dim gapped Dirac cone

* gap is induced by SOC

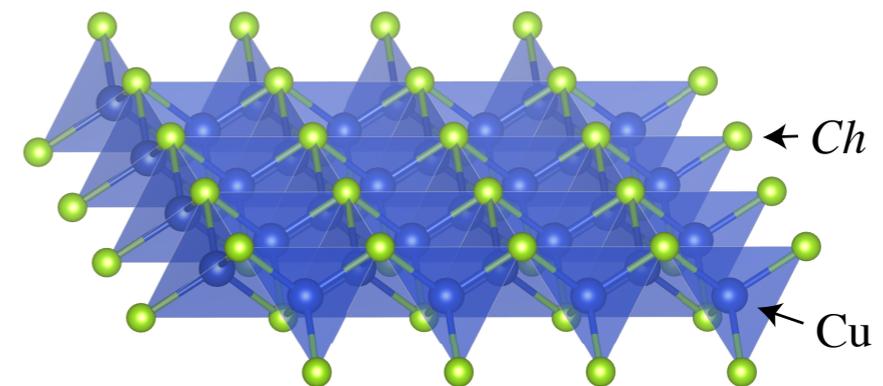


Ta₄SiTe₄

T. Inohara *et al.*, APL **110**, 183901 (2017).



Low-dim. in the CuCh (Ch = S, Se) layer

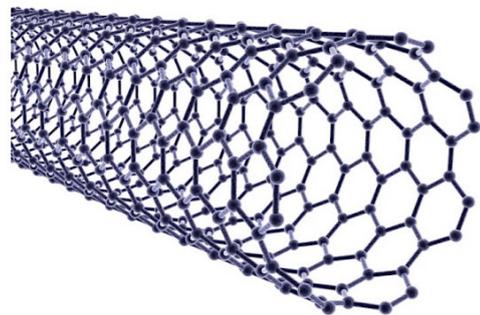


hidden 1-dim network on the square lattice
→ similarity to BiS₂ systems

MO *et al.*, PRMater. **2**, 085401 (2018).

Relation to other thermoelectric materials

Carbon nanotube



1dim (gapped) Dirac cone

high mobility but high thermal conductivity

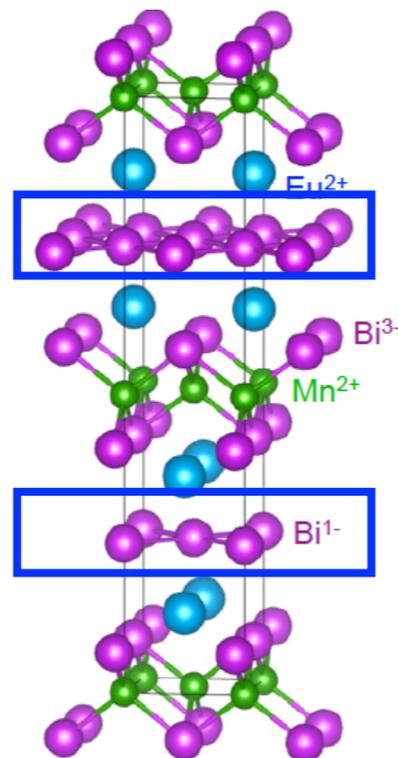
R. S. Prasher *et al.*, PRL **102**, 105901 (2009). Y. Nakai *et al.*, Appl. Phys. Express **7**, 025103 (2014). T. Yamamoto and H. Fukuyama, JPSJ **87**, 024707 (2018); *ibid.* 114710 (2018).

AMnBi₂ (A = Ca, Sr, Eu)

also have a $p_{x,y}$ network on the Bi square lattice

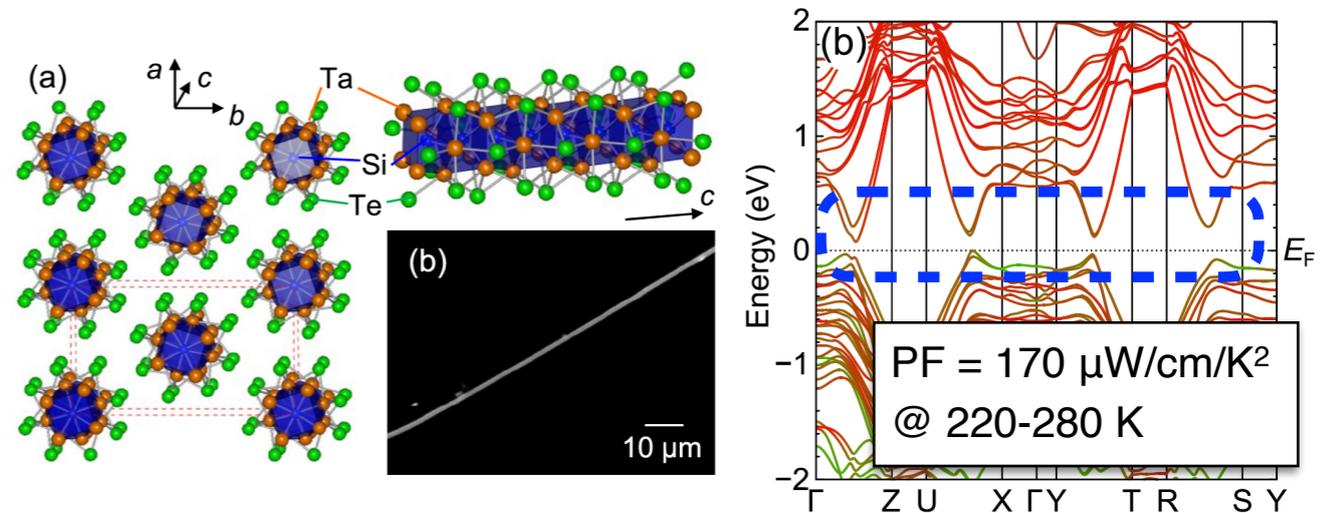
→ quasi-1dim gapped Dirac cone

* gap is induced by SOC

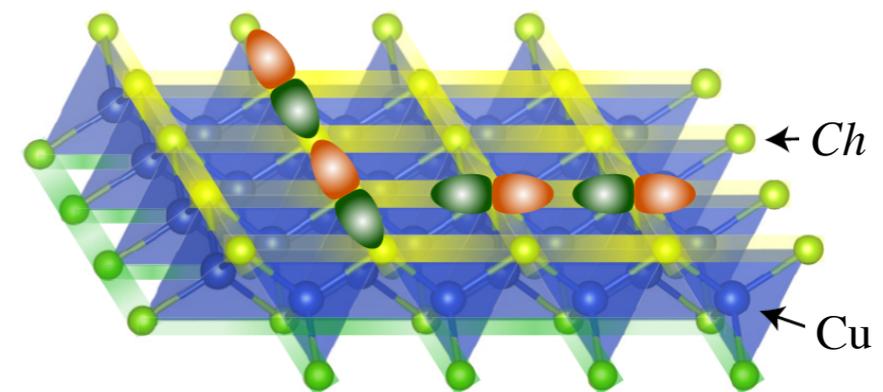


Ta₄SiTe₄

T. Inohara *et al.*, APL **110**, 183901 (2017).



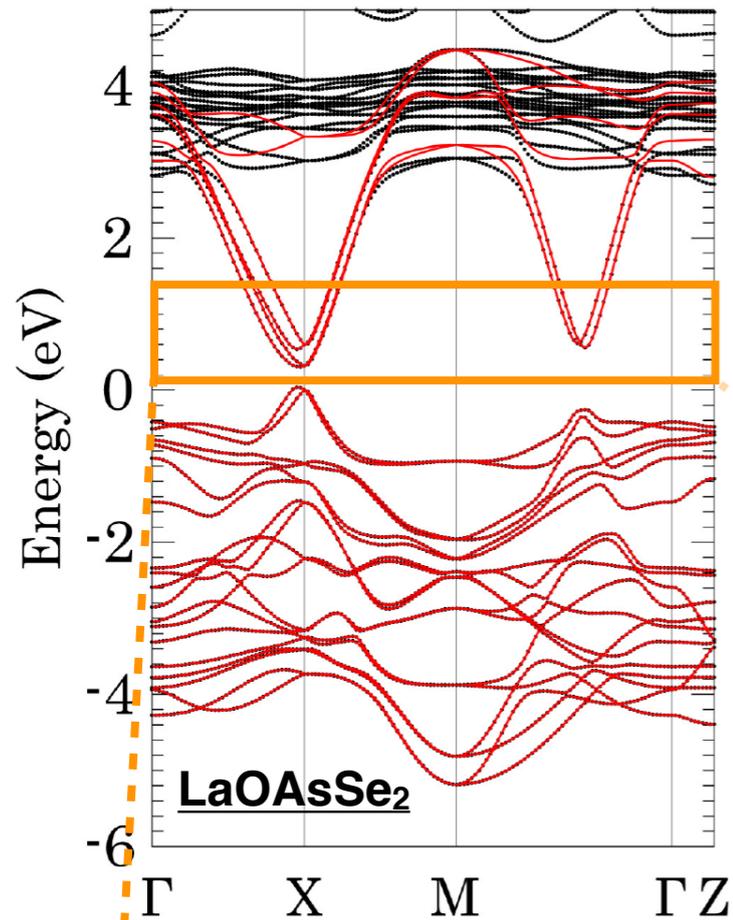
Low-dim. in the CuCh (Ch = S, Se) layer



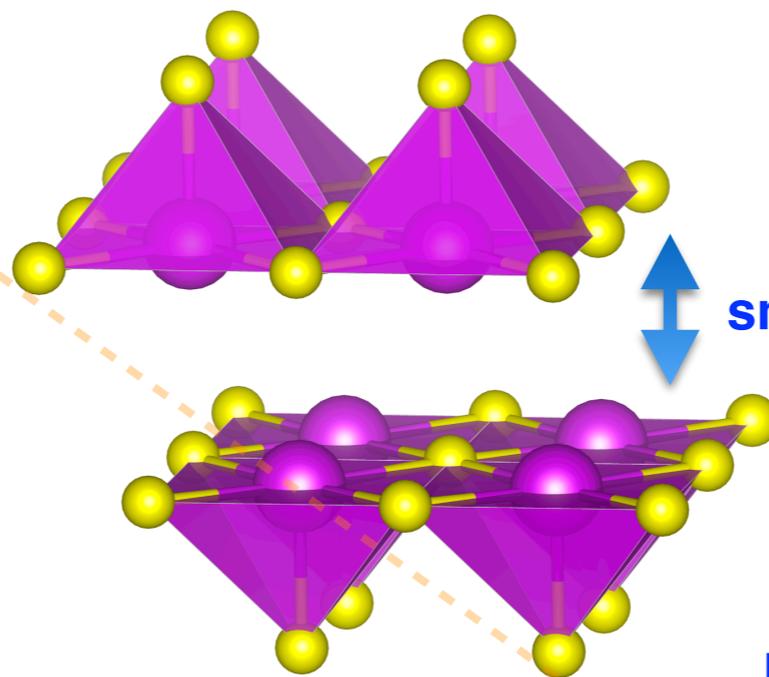
hidden 1-dim network on the square lattice
→ similarity to BiS₂ systems

MO *et al.*, PRMater. **2**, 085401 (2018).

Another important factor: quantum interference



quantum interference is another key for multi-valley

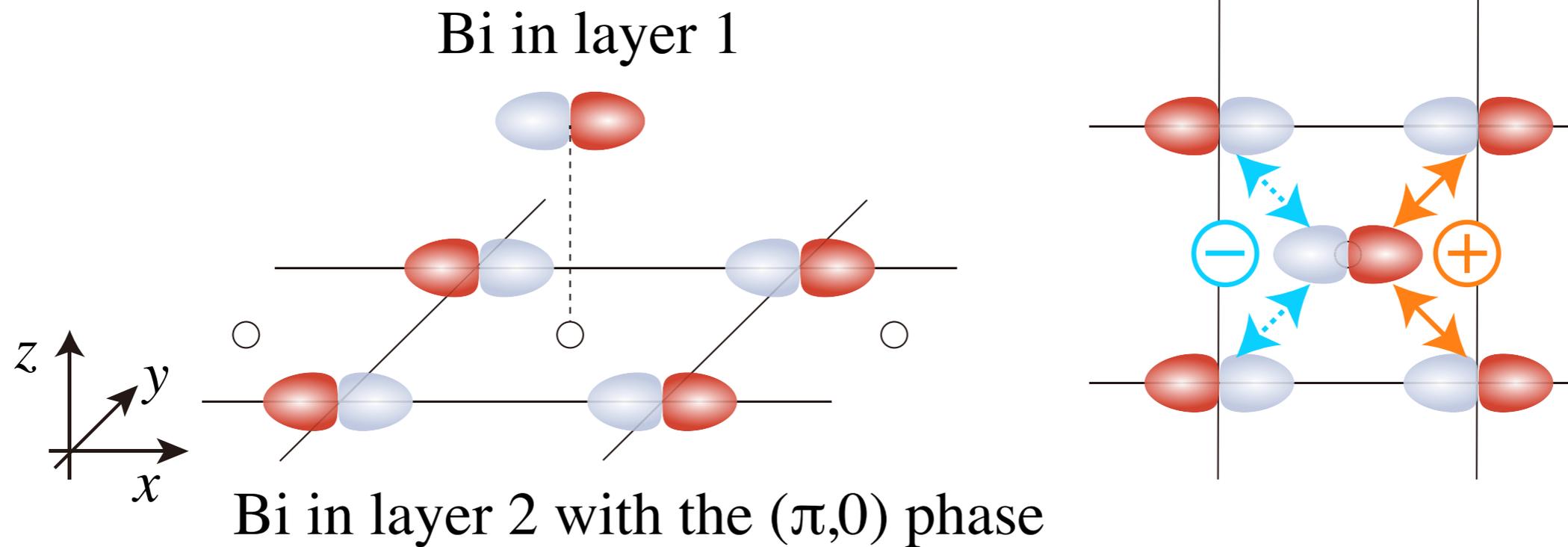


Why suppressed (prohibited)?

= quantum interference



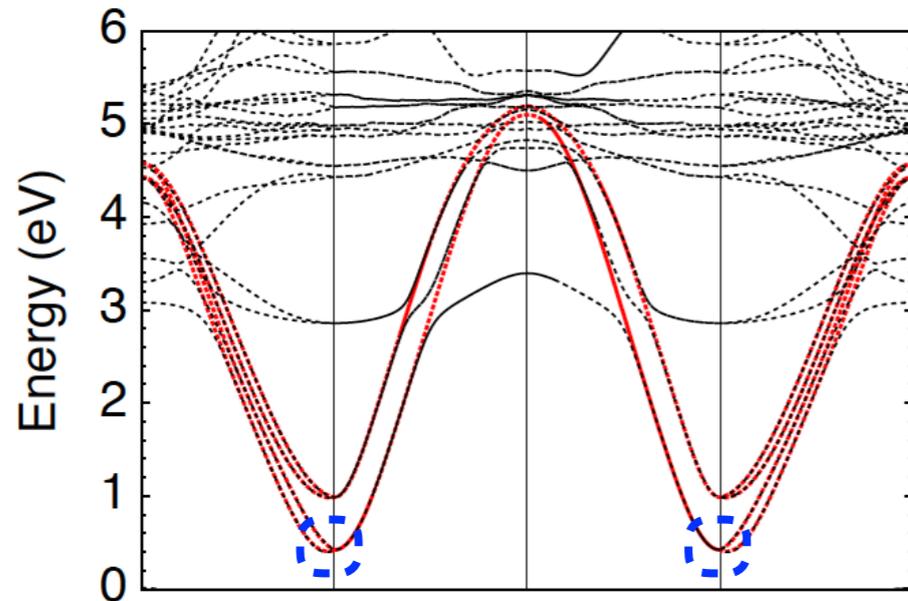
Orbital symmetry and quantum interference



Inter-layer coupling is prohibited at the $X = (\pi, 0)$ point by symmetry

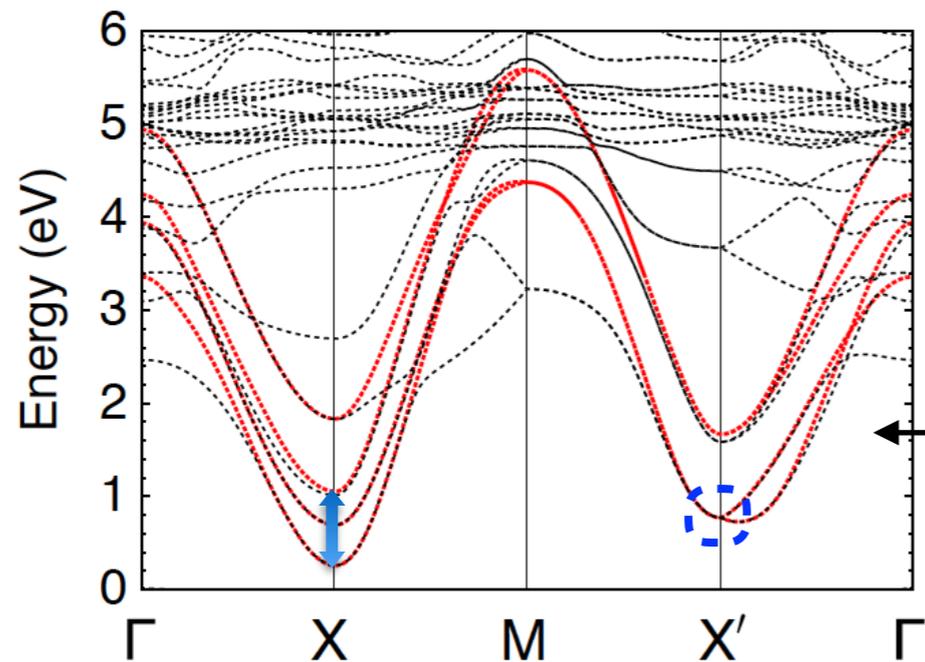
Band-edge degeneracy by quantum interference

(a) Tetragonal w/o SOC



Symmetry forbids the band splitting at X
→ band-edge degeneracy (multi-valley)

(c) Monoclinic w/o SOC

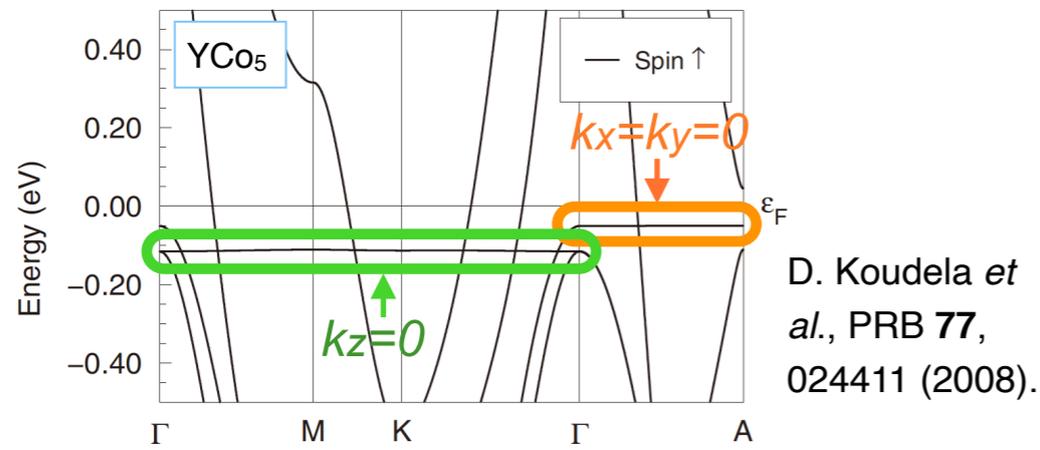


← at 3.8 GPa, with monoclinic distortion

: symmetry lowering allows band splitting

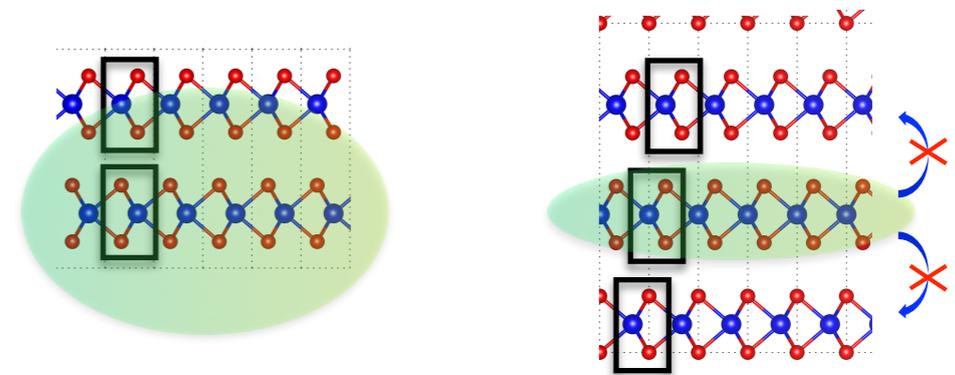
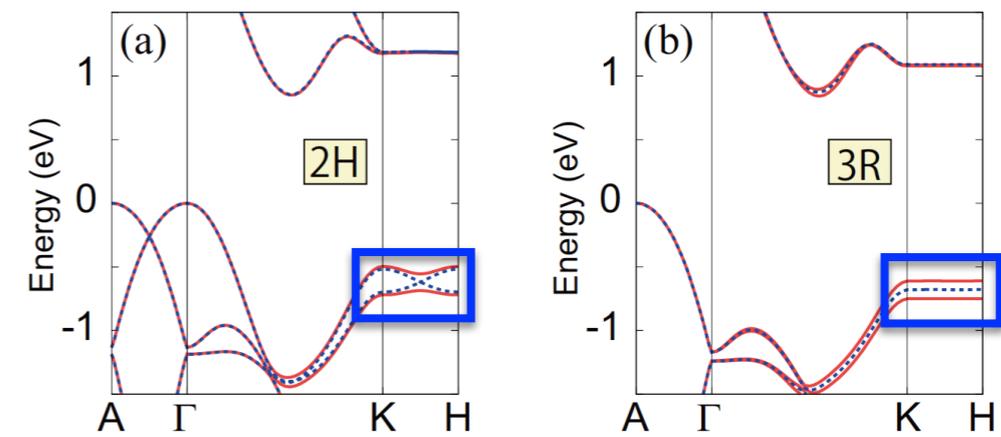
Quantum interference and materials functionalities

flat band and ferromagnetism



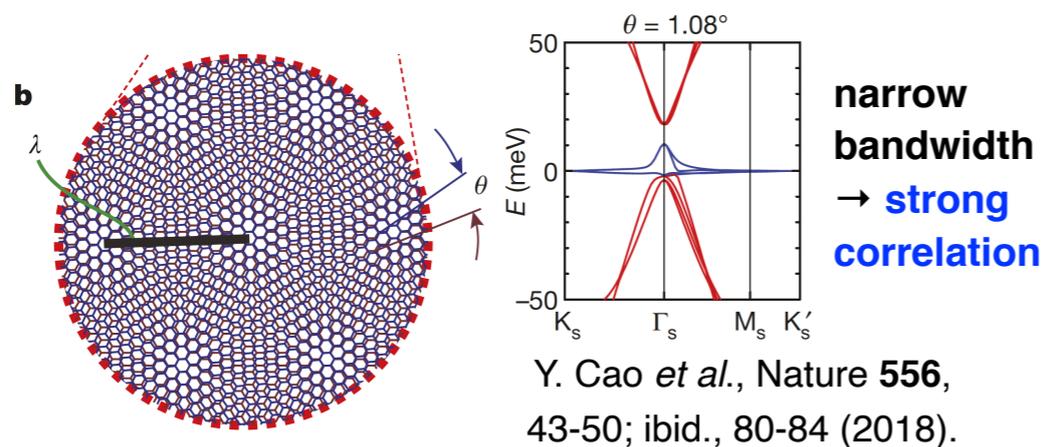
MO *et al.*, PRB **91**, 165137 (2015).

exciton confinement for MoS₂



R. Akashi, **MO**, *et al.*, PRAppI. **4**, 014002 (2015).

Twisted bilayer graphene



MO *et al.*, PRB **98**, 081102(R) (2018).

Toward experimental realization of high-thermoelectric performance

$Ln(O,F)SbSe_2$ ($Ln = La, Ce$)

Y. Goto *et al.*, JPSJ **87**, 074703 (2018).

Low $\kappa = 0.8$ W/m/K for Ce

but carrier doping is very difficult

→ high $\rho > 10^0$ Ωm @ room temperature

14 Si ケイ素 28.085	15 P リン 30.974	16 S 硫黄 32.06	17 Cl 塩素 35.45	18 Ar アルゴン 39.948
32 Ge ゲルマニウム 72.630	33 As ヒ素 74.922	34 Se セレン 78.971	35 Br 臭素 79.904	36 Kr クリプトン 83.798
50 Sn スズ 118.71	51 Sb アンチモン 121.76	52 Te テルル 127.60	53 I ヨウ素 126.90	54 Xe キセノン 131.29
82 Pb 鉛 207.2	83 Bi ビスマス 208.98	84 Po ポロニウム (209)	85 At アスタチン (210)	86 Rn ラドン (222)
114	115	116	117	118

Future issues:

(1) **Carrier control**

(2) **monoclinic instability**

Bi → Sb induces monoclinic instability and then the thermoelectric performance can be degraded

Also F substitution (for carrier doping) becomes difficult by monoclinic distortion

calc : N. Hirayama, MO, *et al.*, PRB **100**, 125201 (2019).

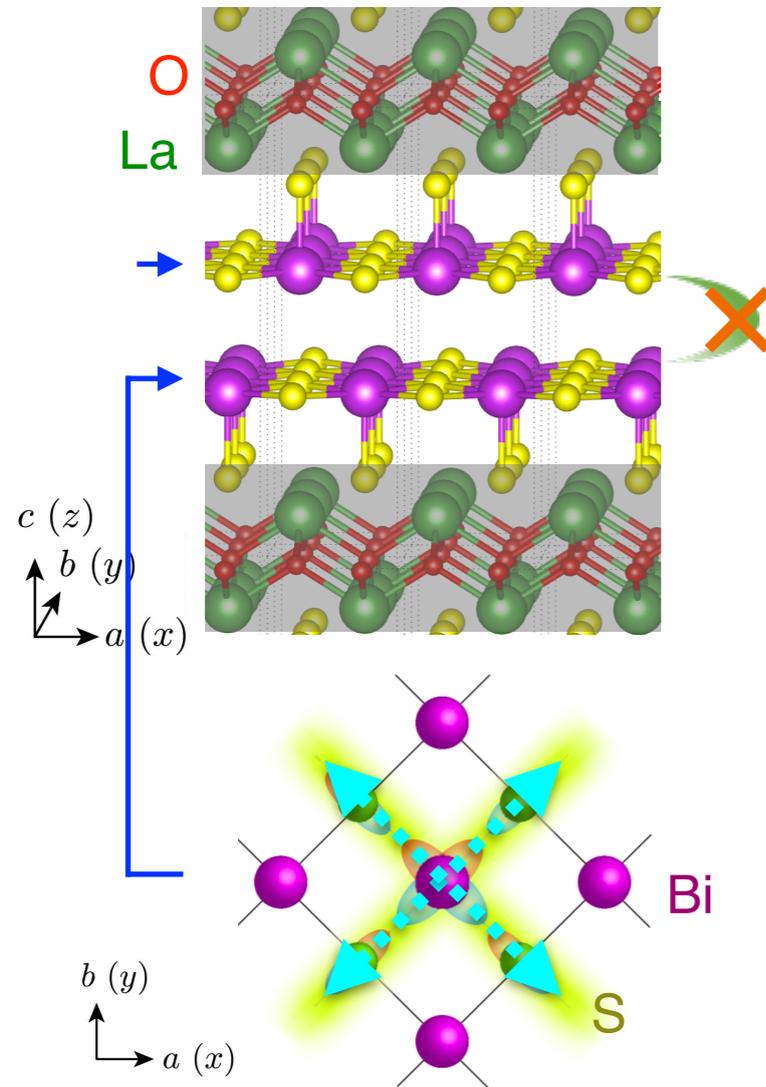
Control the blocking layer?

4-layer systems? → tetragonal becomes stable

cf.) material design of 4-layer systems:

K.Kurematsu, MO, *et al.*, JPSJ **89**, 024702 (2020).

Summary of Part 1



- 1) Insulating layer : suppress coupling along z-direction
- 2) quant. interference : suppress bilayer coupling
- 3) Orbital anisotropy on the square lattice : quasi-1D
(controllable dimensionality by atomic substitution)

q1D gapped Dirac cone = ideal band structure
(low-dim + high group velocity + multi-valley)

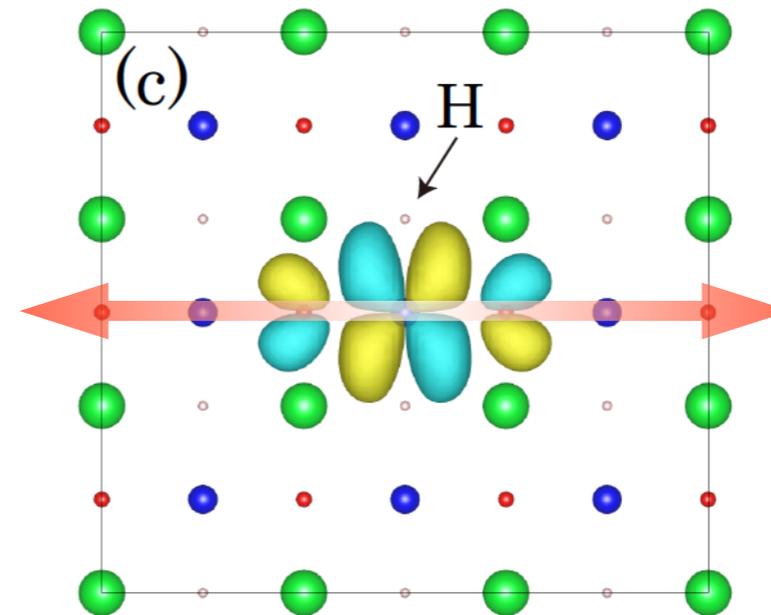
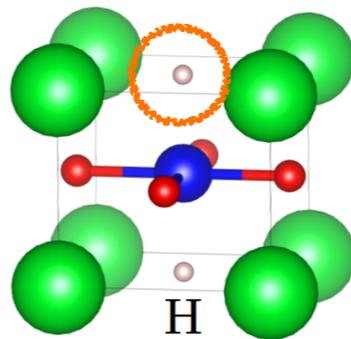
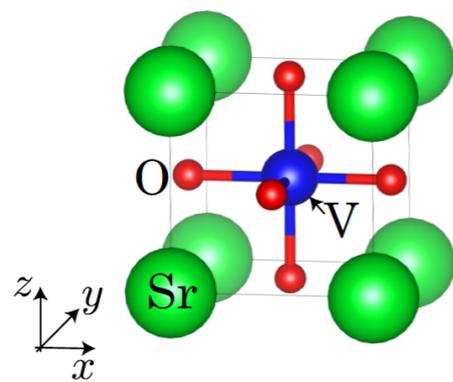
[Refs]

MO, R. Akashi, and K. Kuroki, JPSJ **85**, 094705 (2016).

MO, H. Usui, and K. Kuroki, Phys. Rev. Appl. **8**, 064020 (2017).

MO, H. Usui, and K. Kuroki, J. Phys. Soc. Jpn. **88**, 041010 (2019). (review)

Part 2 : Possible superconductivity in transition-metal oxyhydrides

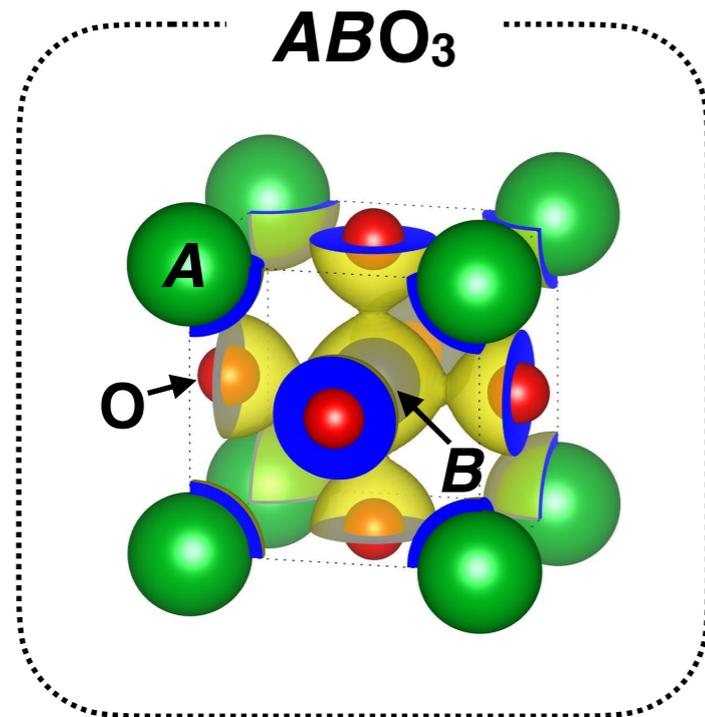


N. Kitamine, **MO**, and K.Kuroki,
arXiv:2007.01553 (2020).

[Collaborators] Naoya Kitamine, Kazuhiko Kuroki (Osaka Univ.)

Transition-metal oxides

Playground of many kinds of intriguing physics
(superconductivity, magnetism, ferroelectricity,...)



A = Ca, Sr, Ba, Y, La, etc.

carrier doping, chemical pressure

B = Transition metal (V, Cr, Mn, Fe, Ru,...)

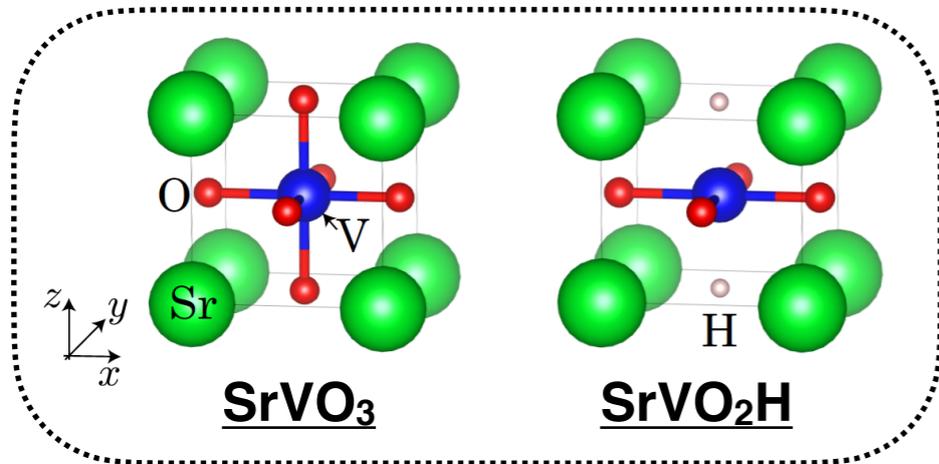
governs materials properties

O → H, F, N, Cl,...

**New degrees of freedom
for material design**

Transition-metal oxyhydrides

Crystal field (environment for cation)

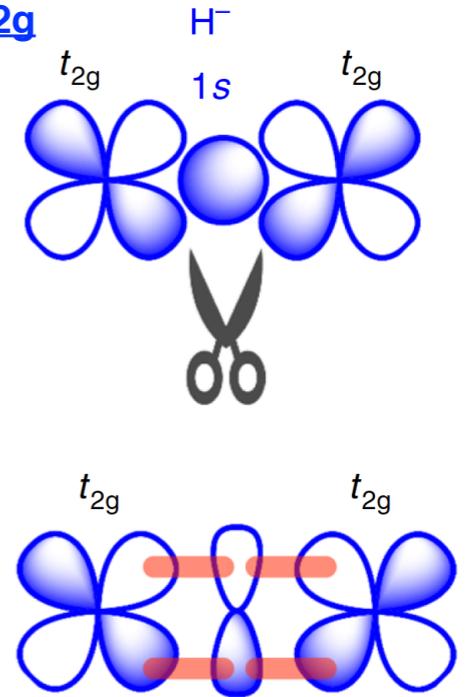


x, y, z
directions are
equivalent

z is inequivalent

Bond breaking between t_{2g}

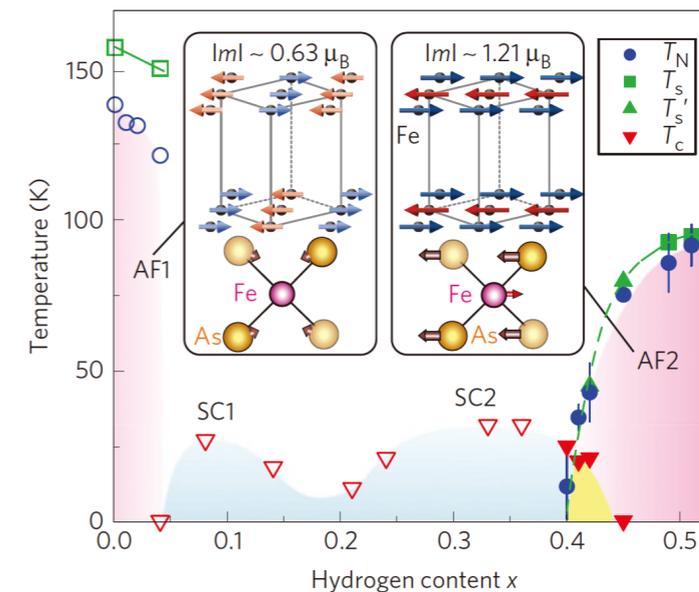
H-s has a different parity to that for M- t_{2g} (d orbital), then breaks a chemical bond between d orbitals



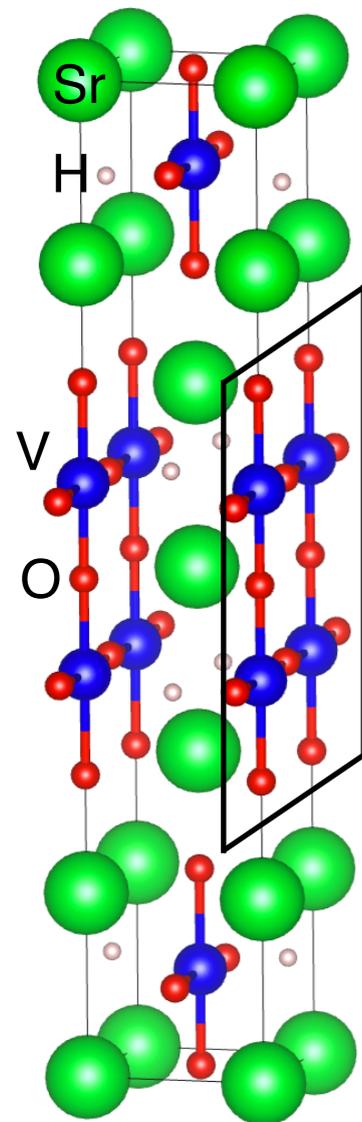
cf.) H. Kageyama *et al.*, *Nature Commun.* **9**, 772 (2018).

Carrier doping by substitute H- for O²⁻

e.g.) LaFeAsO_{1-x}H_x: S. Iimura *et al.*, *Nature Commun.* **3**, 943 (2012); M. Hiraishi *et al.*, *Nature Phys.* **10**, 300 (2014). (Fig.)



Theoretical proposal for unconventional superconductivity



Ladder structure

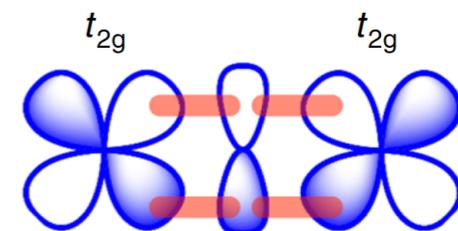
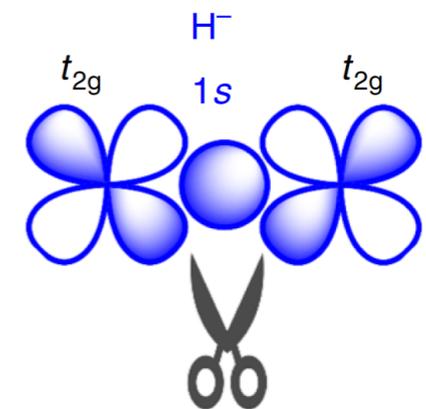
→ **unconventional superconductivity?**

- E. Dagotto *et al.*, *Phys. Rev. B* **45**, 5744 (1992).
- T. M. Rice *et al.*, *EPL* **23**, 445 (1993).
- E. Dagotto and T. M. Rice, *Science* **271**, 618 (1996).
- K. Kuroki *et al.*, *Phys. Rev. B* **72**, 212509 (2005).
- D. Ogura *et al.*, *Phys. Rev. B* **96**, 184513 (2017).

We investigate whether this material can host superconductivity by theoretical calculation

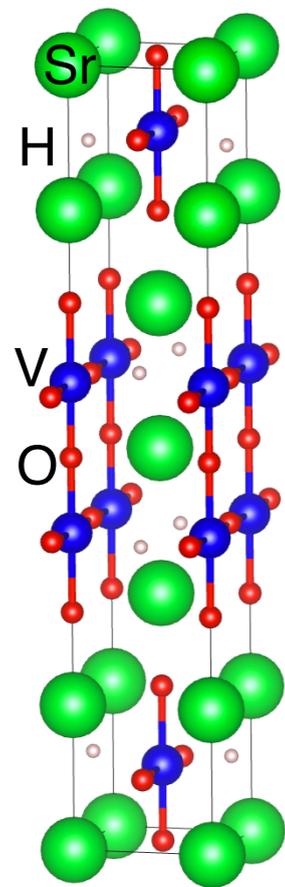


Naoya Kitamine



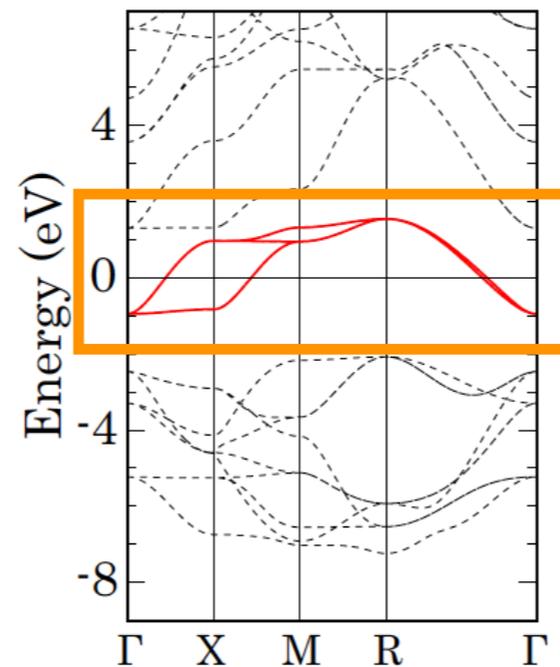
Method: First-principles calculation and an effective model

Crystal structure



First-principles band structure

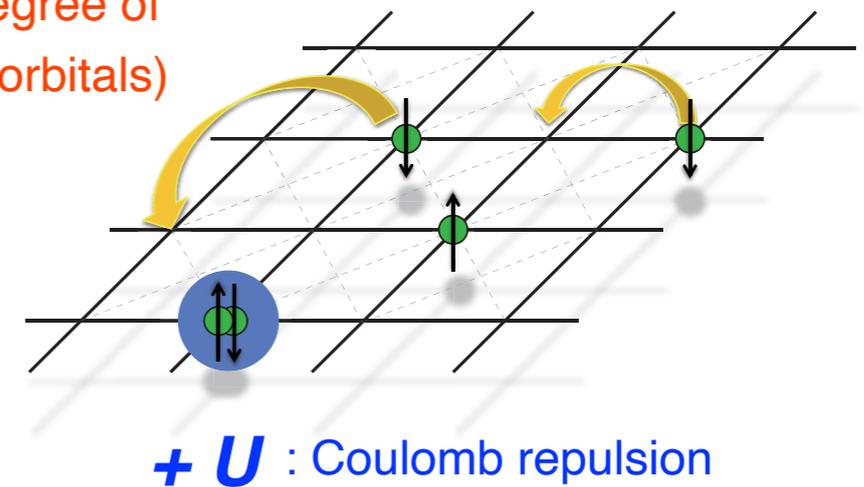
PBE+GGA (WIEN2k)



Effective model consisting of Wannier functions

Wannier90

a small degree of freedom (orbitals)

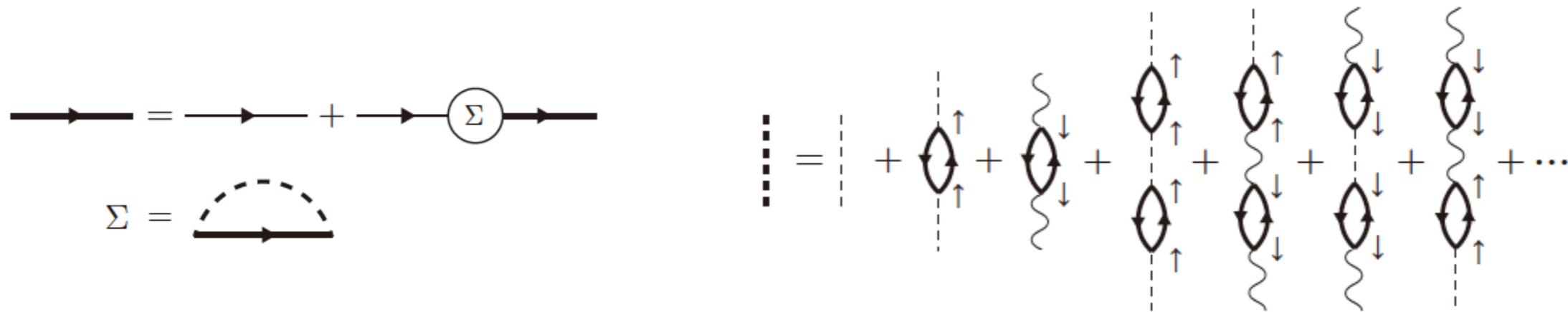


$$H = \sum_{i,j,\sigma} t_{ij} \hat{c}_{i,\sigma}^\dagger \hat{c}_{j,\sigma} + \sum_i U_i \hat{n}_{i,\uparrow} \hat{n}_{i,\downarrow}$$

Hubbard model

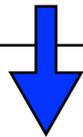
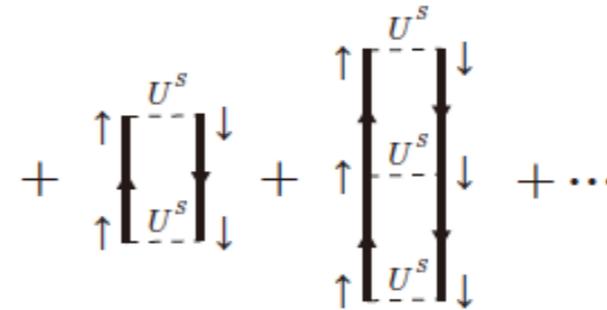
By using the effective model, we can consider strong electron correlation

Method: FLEX + linearized Eliashberg eq.



Fluctuation exchange (FLEX) approx.:

determine self-energy (energy correction by U)
by considering ring & ladder diagram



Linearized Eliashberg eq. :

$\lambda = 1$ means superconducting (SC)
transition

In real calculation, we fix the
temperature and see λ as a
measure of how superconductivity
is favored in this system

$$\lambda \Delta_{ll'}(k) = -\frac{T}{N} \sum_q \Gamma_{lm_1m_4l'}^s(k-q) G_{m_1m_2}(q) G_{m_4m_3}(-q) \Delta_{m_2m_3}(q)$$

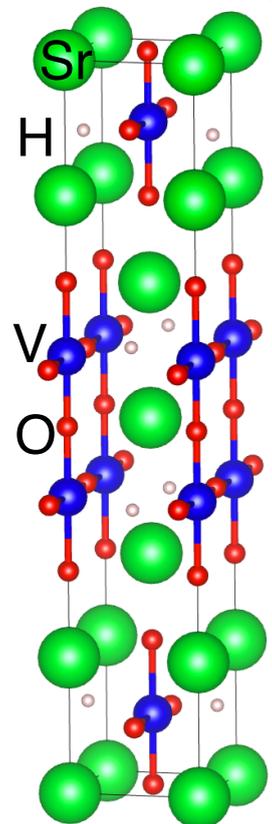
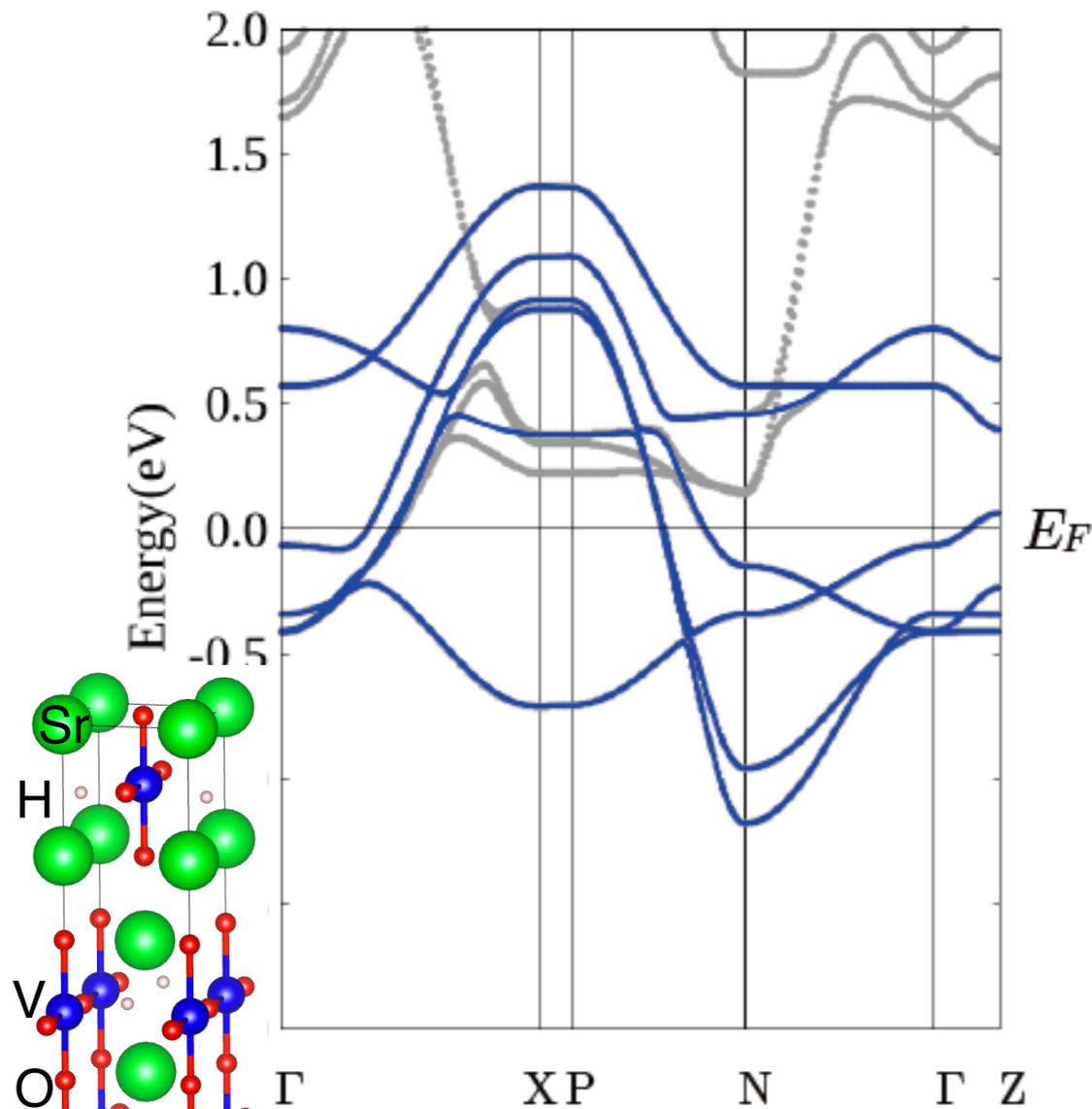
$\Delta_{ll'}(k)$: gap 関数

$$\Gamma^s(k) = U + \frac{3}{2} U \chi^{sp}(k) U - \frac{1}{2} \chi^{ch}(k) U: \text{有効相互作用}$$

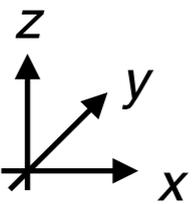
$$\chi^{sp} = \chi^0 / (1 - U \chi^0), \quad \chi^{ch} = \chi^0 / (1 + U \chi^0): \text{スピン/電荷感受率}$$

$$\chi_{m_1m_2m_3m_4}^0(q) = -\frac{T}{N} \sum_k G_{m_3m_1}(k+q) G_{m_2m_4}(k): \text{既約感受率}$$

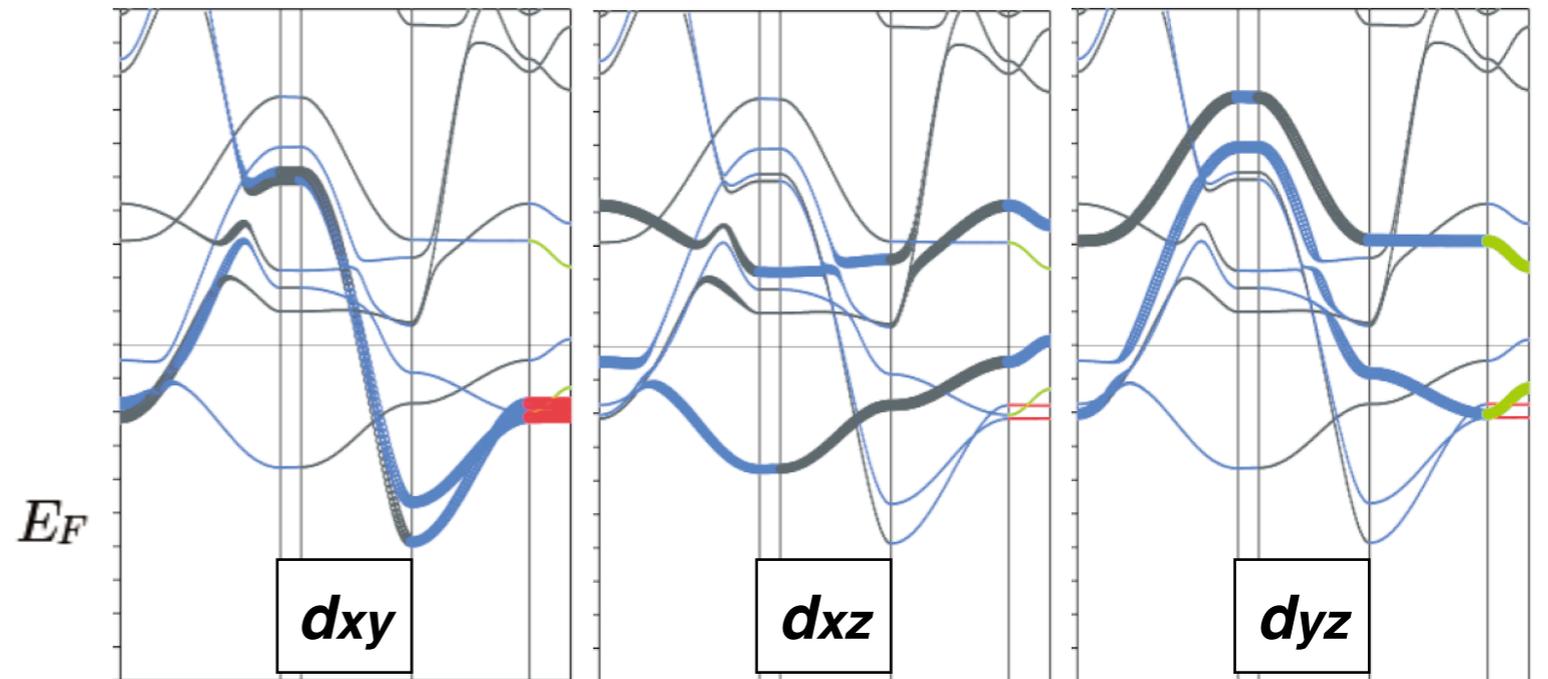
Band structure: $\text{Sr}_3\text{V}_2\text{O}_5\text{H}_2$



H is aligned along the x direction



$X = (\pi, \pi, 0)$, $P = (\pi, \pi, \pi)$, $N = (\pi, 0, \pi)$, $Z = (0, 0, \pi)$ in cartesian

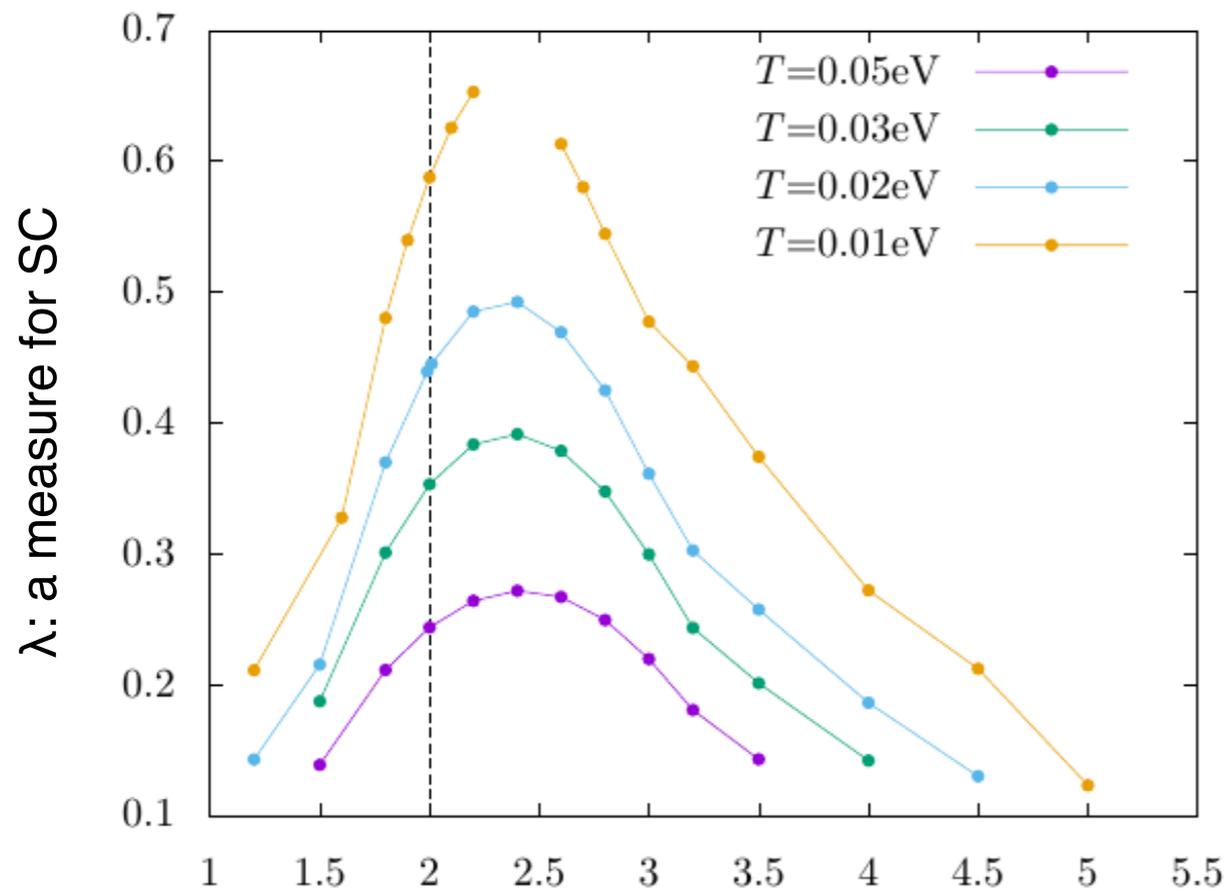


No bilayer splitting

Both d_{xz} and d_{yz} form two-leg ladders

* bonding and anti-bonding bands are characteristic in a two-leg ladder

FLEX + Eliashberg: $\text{Sr}_3\text{V}_2\text{O}_5\text{H}_2$

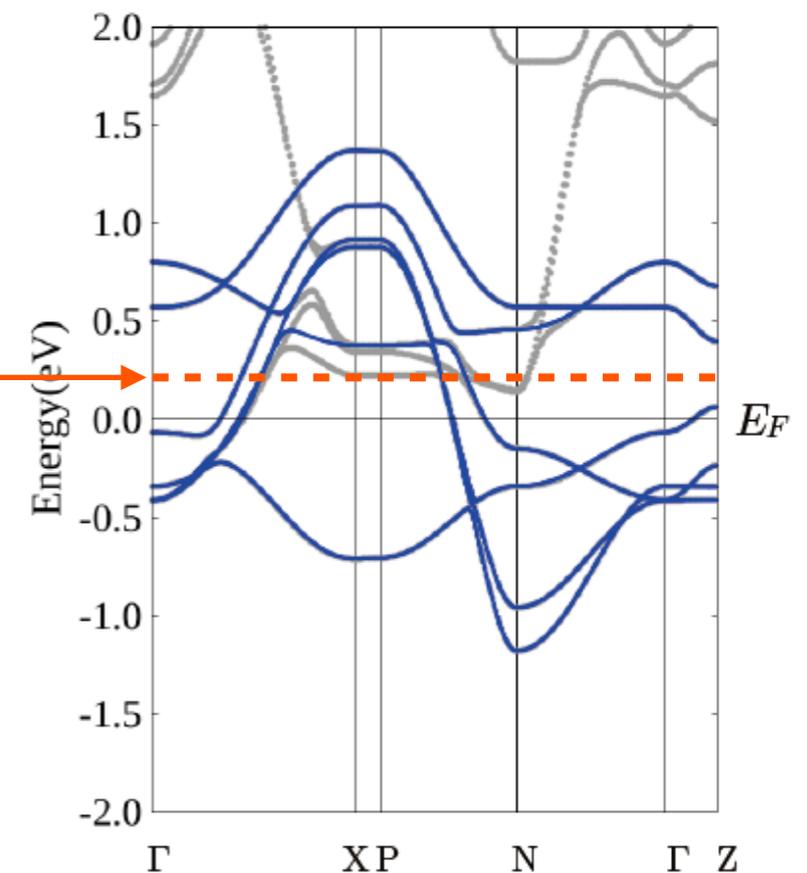


Small electron doping yields a high λ
(comparable to some cuprates!)

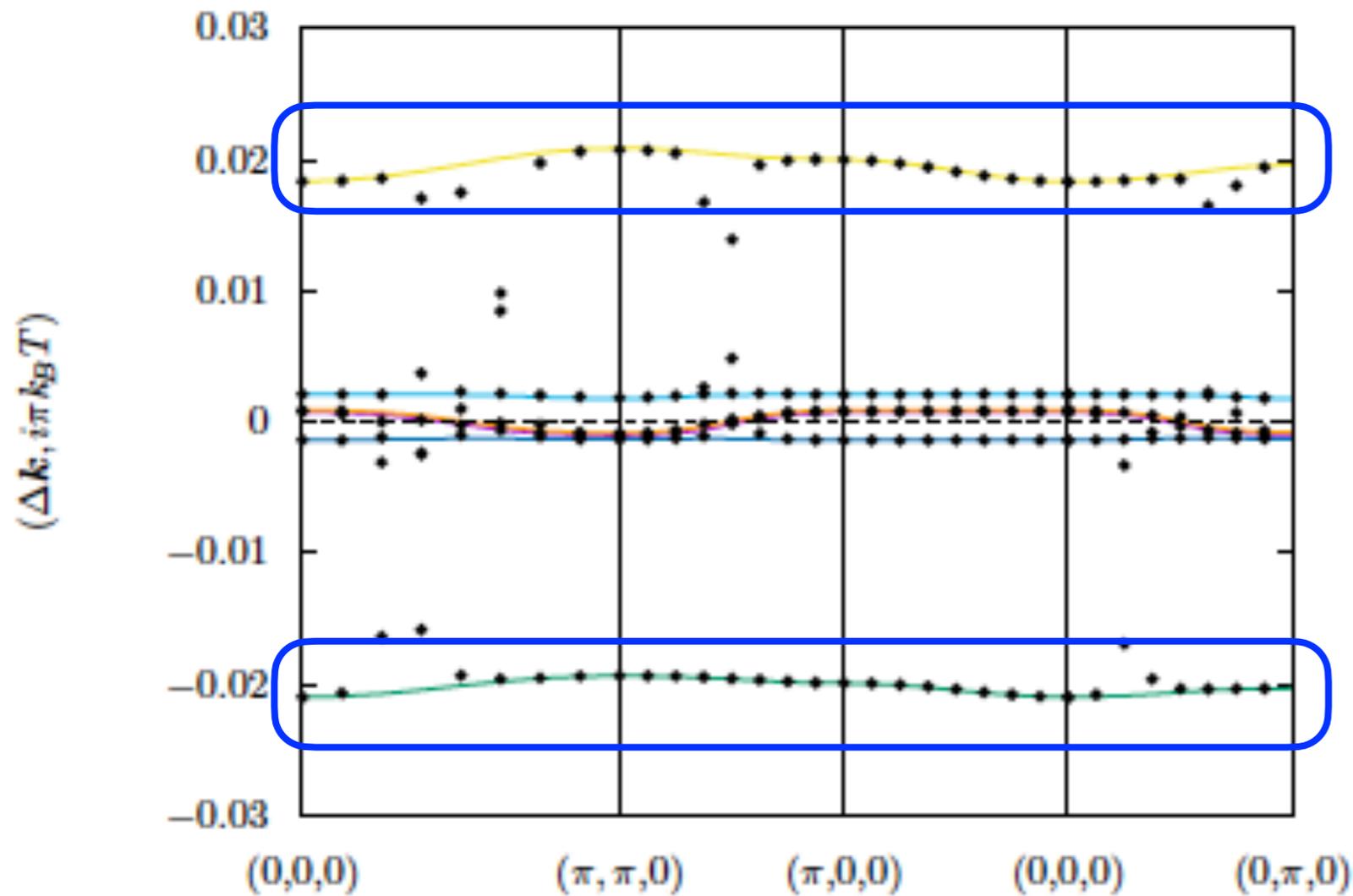
$$U = 2.5 \text{ eV}, J = J' = U/8, U' = U - 2J$$

number of d electrons per vanadium (2 = non-doped)

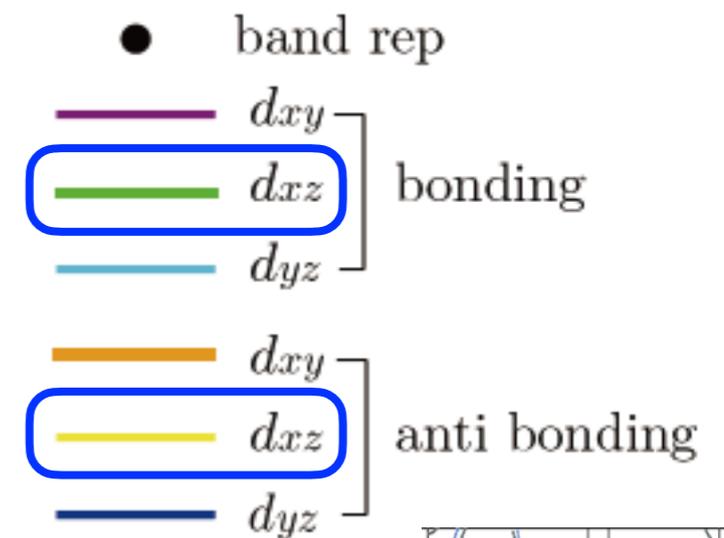
chemical potential for optimal doping



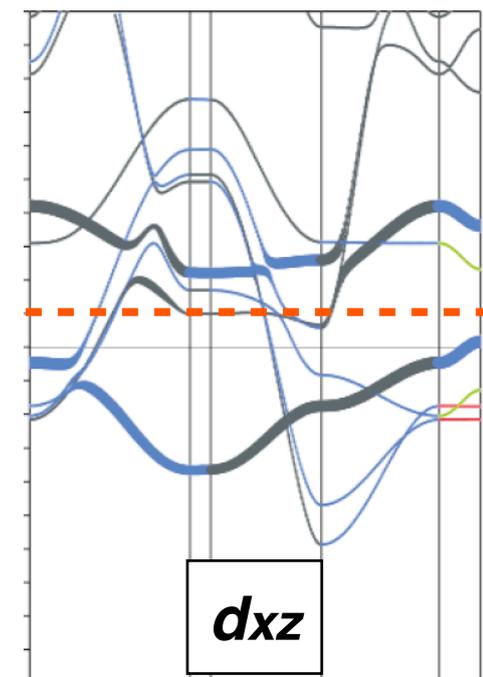
gap function: $\text{Sr}_3\text{V}_2\text{O}_5\text{H}_2$



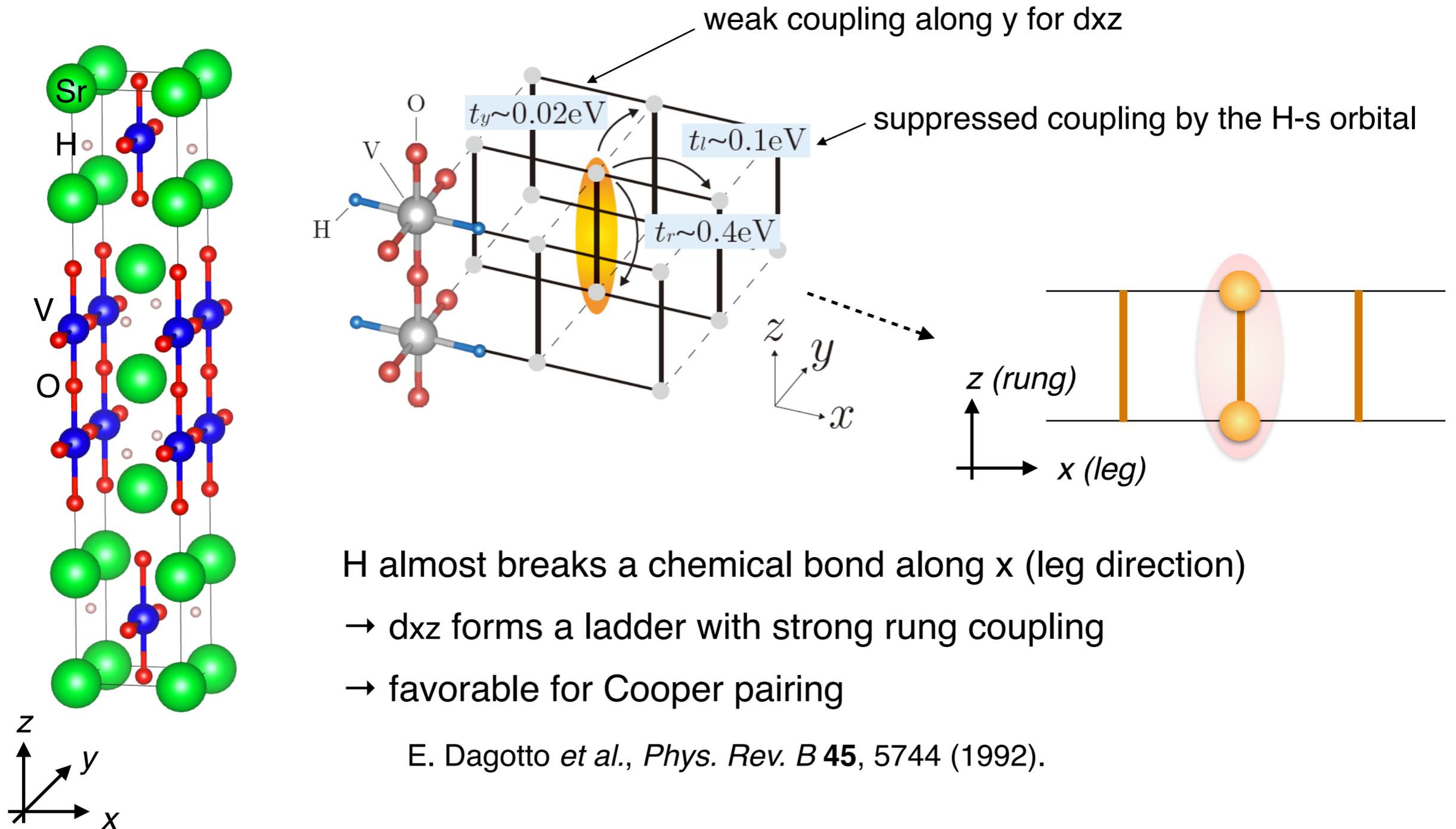
[$T = 0.02$ eV, $n = 2.4$]



- dxz is a key for this superconductivity
- Sign change between bilayer-split dxz bands

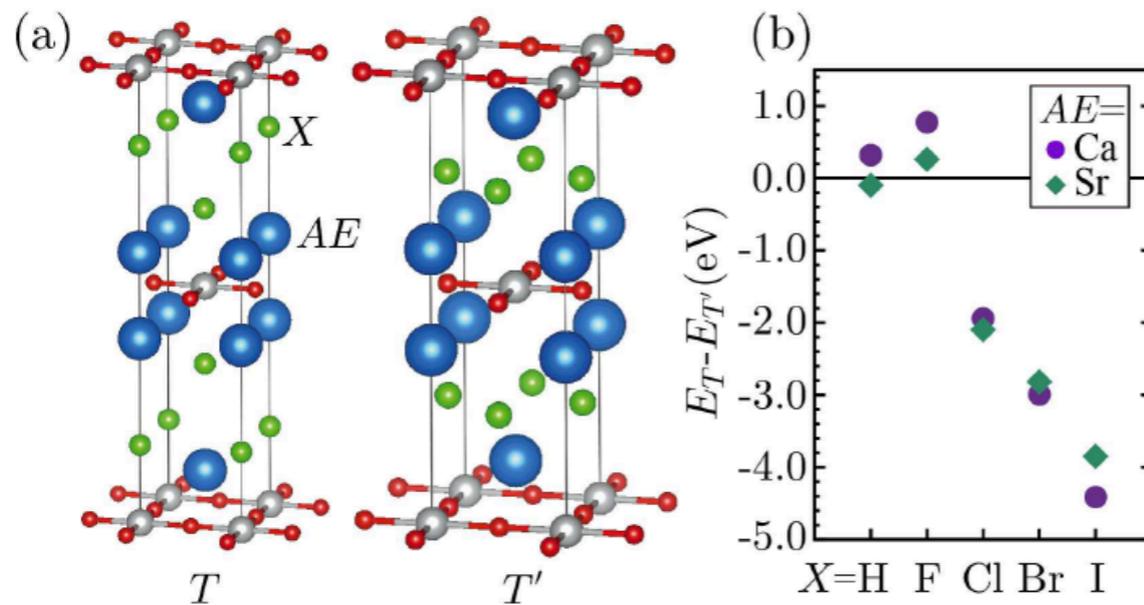


ladder-like electronic states in $\text{Sr}_3\text{V}_2\text{O}_5\text{H}_2$

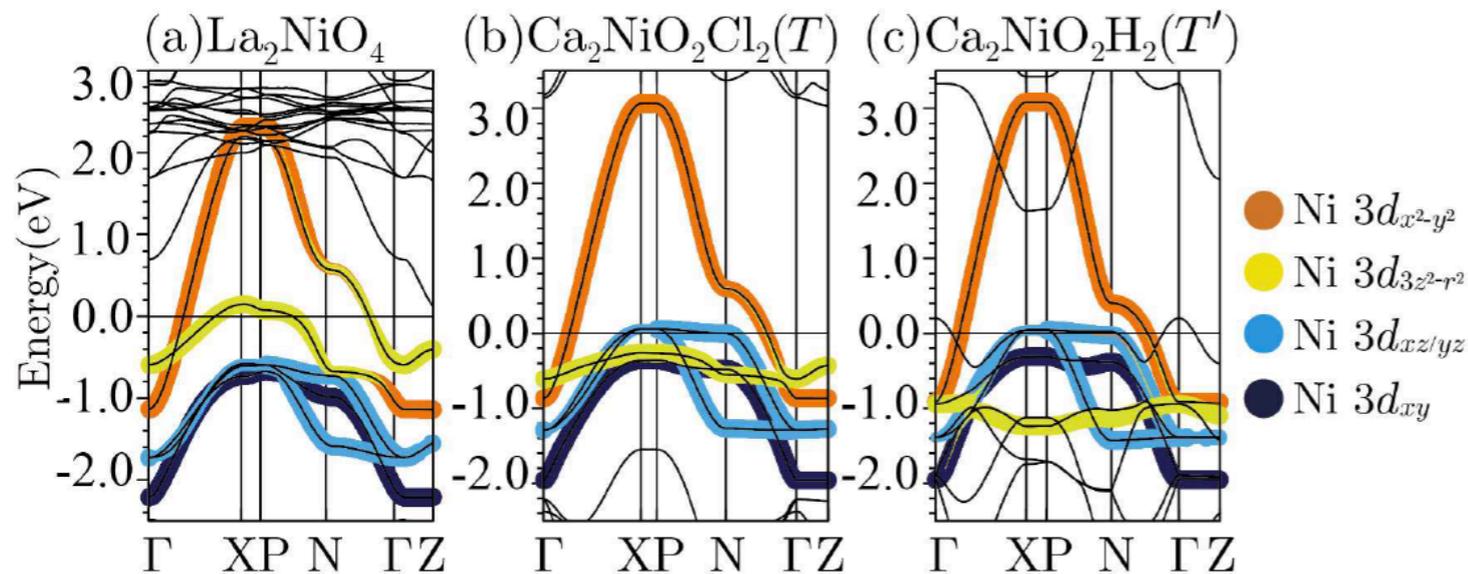


Another candidate: $A_2NiO_2X_2$ ($A = Ca, Sr$; $X = H, F, Cl, etc.$)

N. Kitamine, **MO**, and K.Kuroki,
arXiv:2007.01553 (2020).



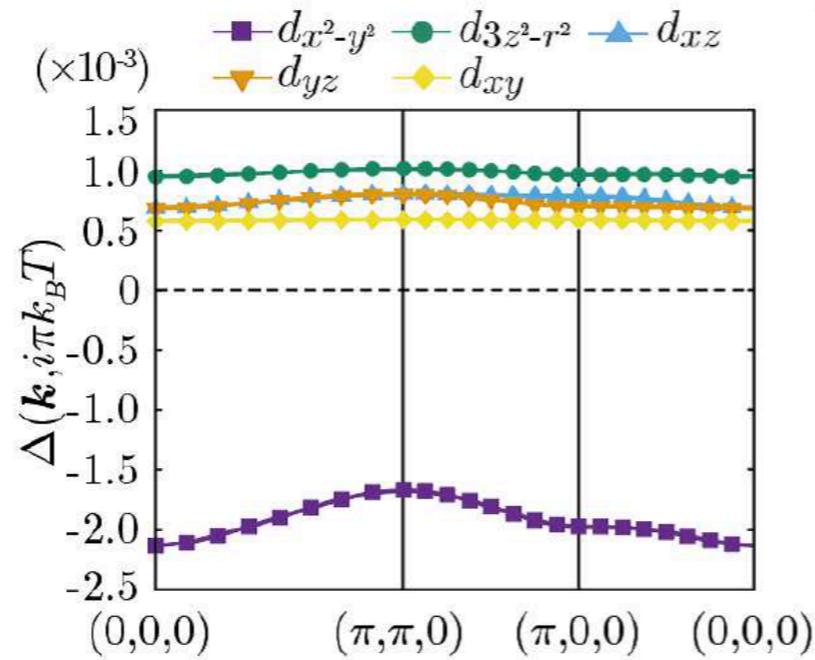
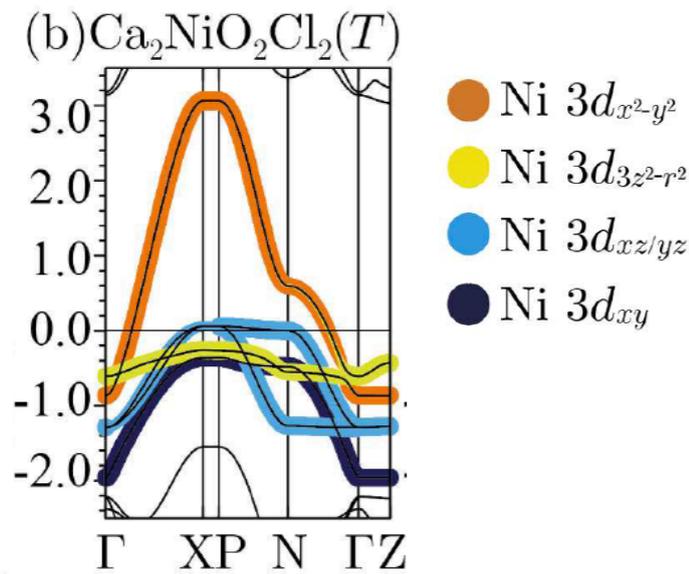
Monolayer systems with apical oxygen
being replaced with other anions



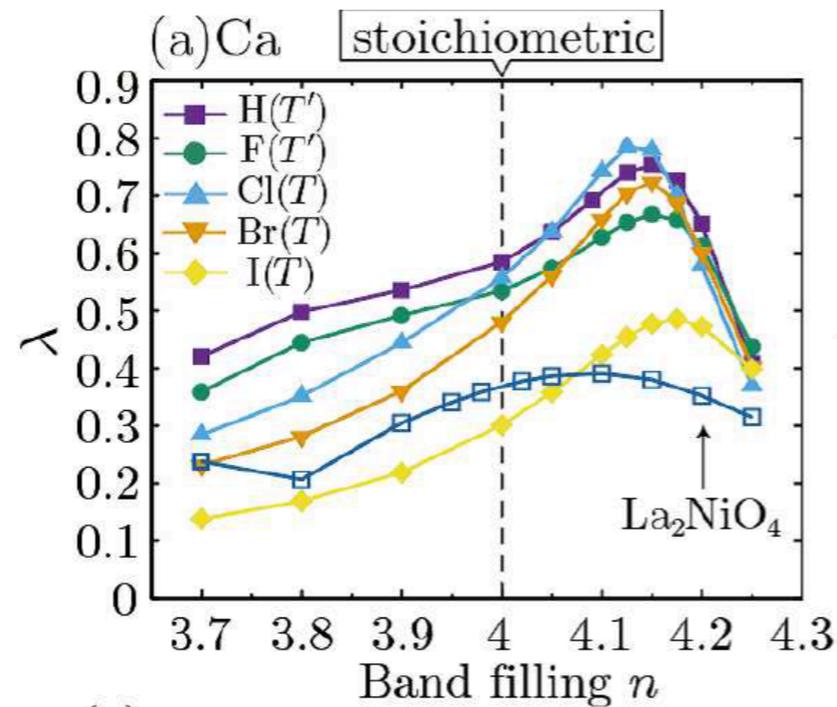
d orbitals other than dx^2-y^2
lie near the Fermi level and acts as
“glue” for Cooper pair of dx^2-y^2

Superconductivity

N. Kitamine, MO, and K.Kuroki,
arXiv:2007.01553 (2020).



Sign change between $d_{x^2-y^2}$ and other d orbitals
 → evidence of a role as “glue”



Electron doping seems necessary

Summary of Part 2

$\text{Sr}_3\text{V}_2\text{O}_5\text{H}_2$ possibly hosts unconventional superconductivity by electron doping, where d_{xz} orbitals form the two-leg ladder with a strong coupling along the rung direction

$\text{A}_2\text{NiO}_2\text{X}_2$ is another candidate where d orbitals other than dx^2-y^2 acts as a glue of Cooper pair of dx^2-y^2 orbital. Here the characteristic crystal field by anion substitution is a key to realize this situation.

* the crystal structure is assumed in this study, so theoretical determination of the anion positions are important future issues. From the experimental viewpoint, the carrier control is also an important issue.

N. Kitamine, **MO**, and K.Kuroki, “*Designing nickelate superconductors with d^8 configuration exploiting mixed-anion strategy*”, arXiv:2007.01553 (2020).